

# Performance of H2GCROC3, the readout ASIC of SiPMs for the back hadronic sections of the CMS High Granularity Calorimeter.

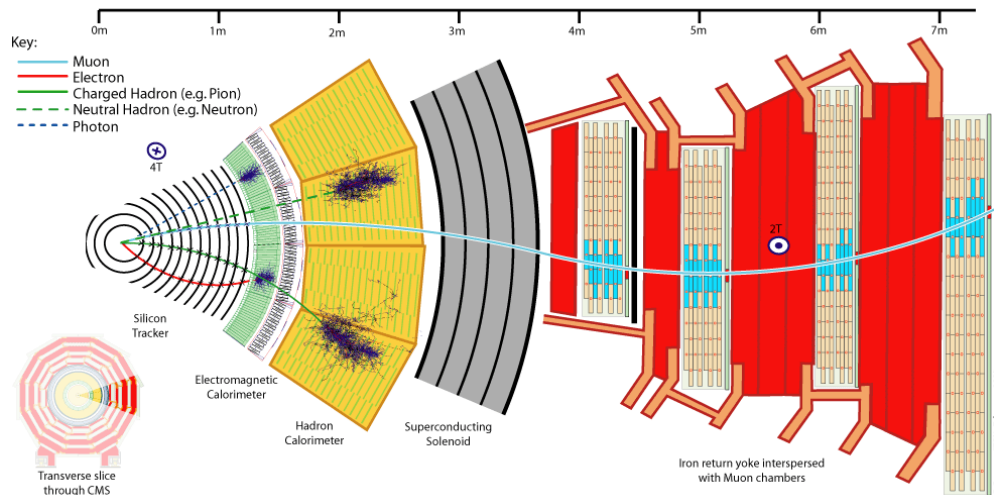
## CMS collaboration

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TWEPP 2023, Topical Workshop on Electronics for Particle Physics.  
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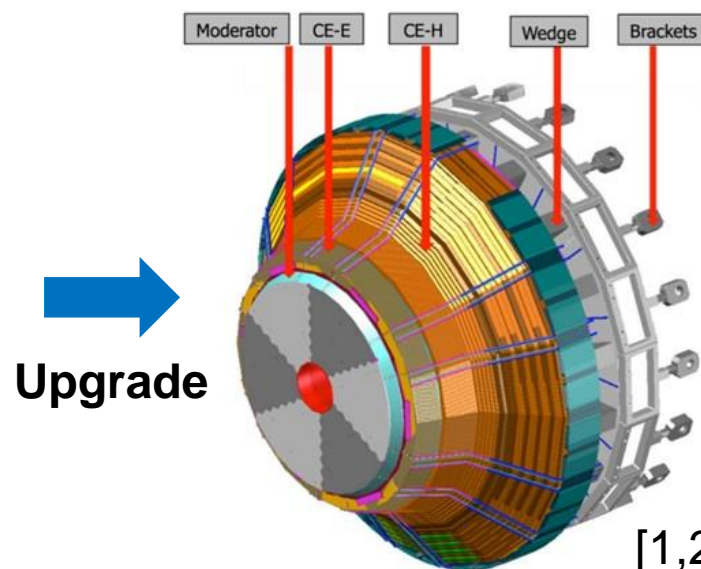


- **Introduction: HGCal**
- **HGCROC**
  - Requirements and Architecture
- **H2GCROC: SiPM version**
  - Requirements and differences
  - Analog channel overview
  - Calibration mode
    - Setup
    - SiPM oscilloscope measurements
    - Single-photon-spectrum
  - Physics mode
    - Setup
    - Measurements
  - Irradiation campaigns and test beam
- **Conclusions**

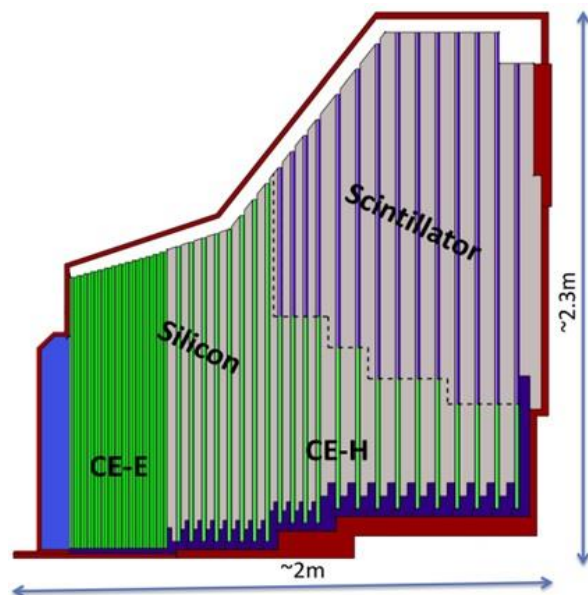


*\*Present endcap calorimeter will not work beyond Run3*

[3]



[1,2]



[5]

	CE-E Silicon	CE-H Silicon	CE-H Scintillator	Total
HGCROC	60 324	31 596	8 496	100 416
Motherboards	5 004	2 556	384	7 944
Bidirectional data/control links	5 004	2 556	384	7 944
Trigger links	4 020	2 556	768	7 344

**Requirement:** Use very similar FE electronics for the readout of both detectors

- Si ( $\sim 4$  fC / MIP)
- SiPM-on-tile ( $\sim 1.7$  pC / MIP) [2]

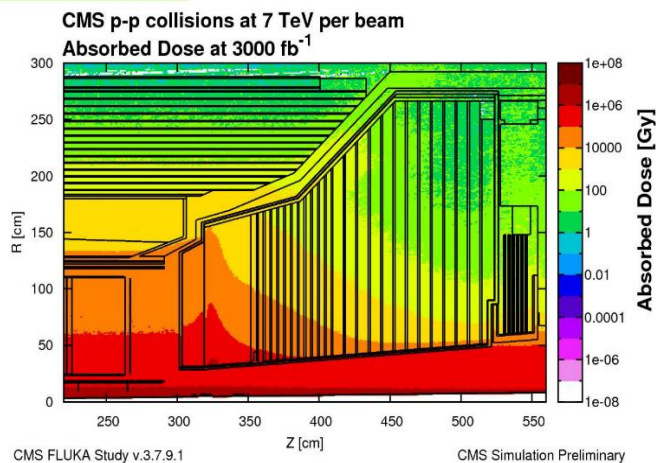
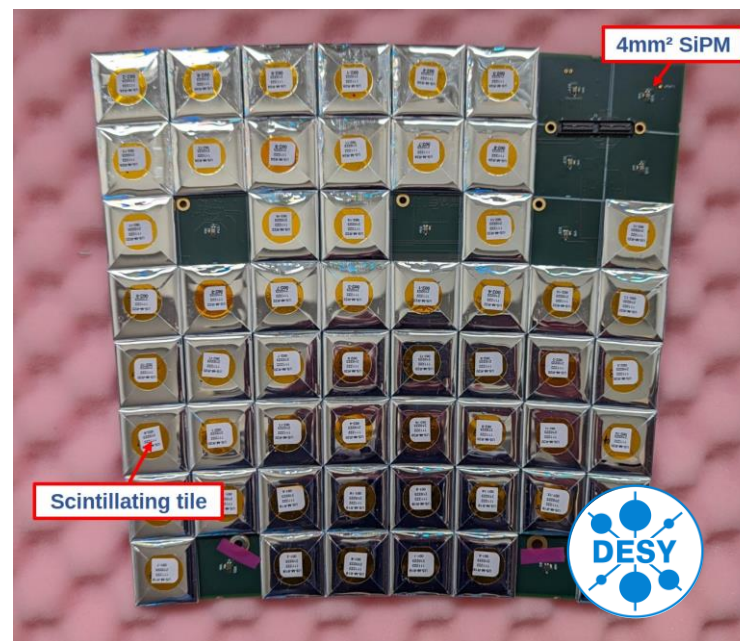
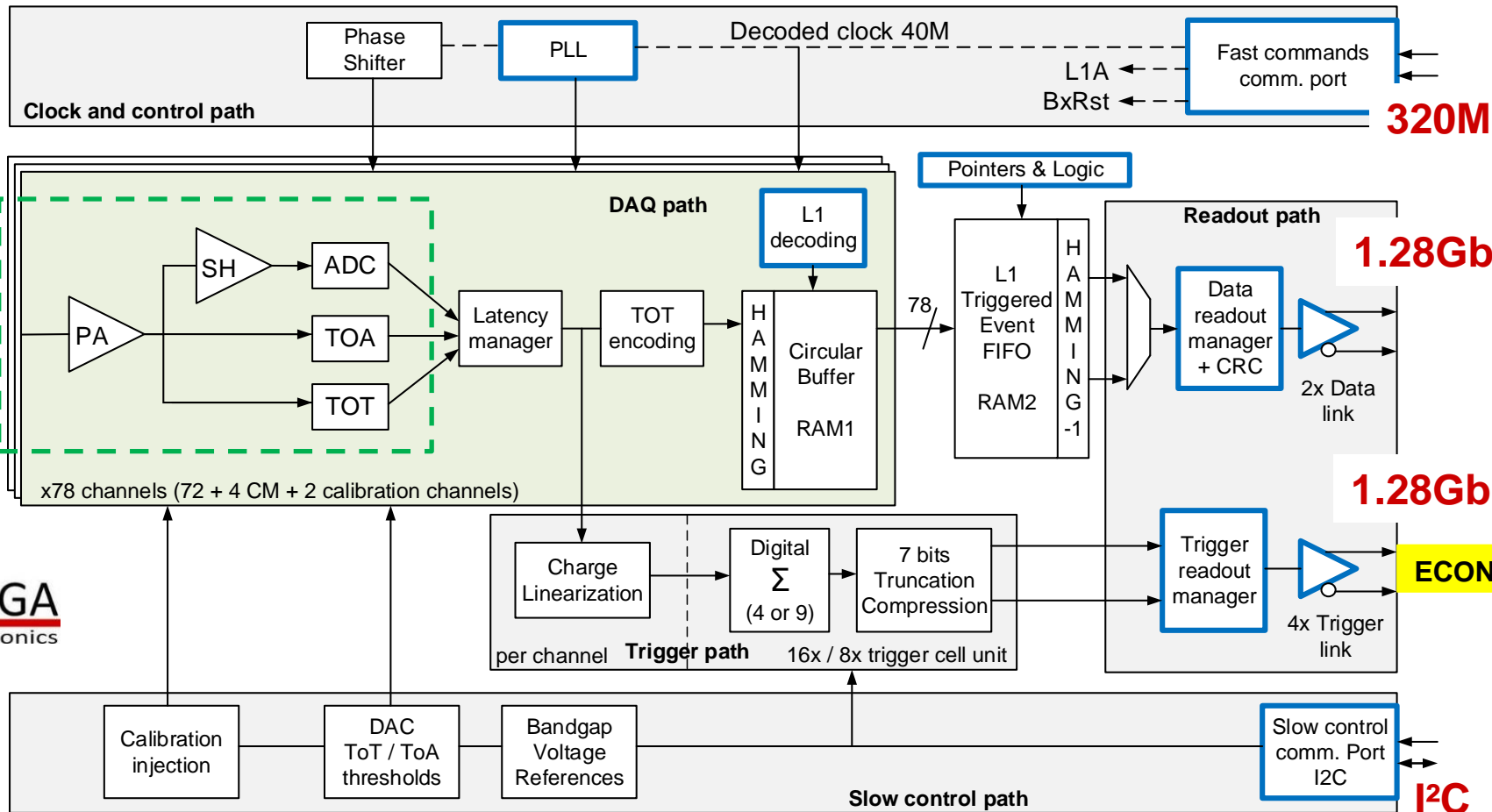


Figure 1.1: Dose of ionizing radiation accumulated in HGCAL after an integrated luminosity of  $3000 \text{ fb}^{-1}$ , simulated using the FLUKA program, and shown as a two-dimensional map in the radial and longitudinal coordinates,  $r$  and  $z$ .

[2]





## Measurements

### • Charge

- ADC (AGH): peak measurement, 10 bits @ 40 MHz, dynamic range defined by preamplifier gain
- TDC (IRFU): TOT (Time over Threshold), 12 bits (LSB = 50ps)
- ADC: 0.25% full range resolution. TOT: 0.025% full range resolution

### • Time

- TDC (IRFU): TOA (Time of Arrival), 10 bits (LSB = 25ps)

\*Next talk: by **Cristina Mantilla**  
\*Tomorrow talk: by **Raghunandan Shukla**

## Requirements for HGCROC (The Si version of the ASIC):

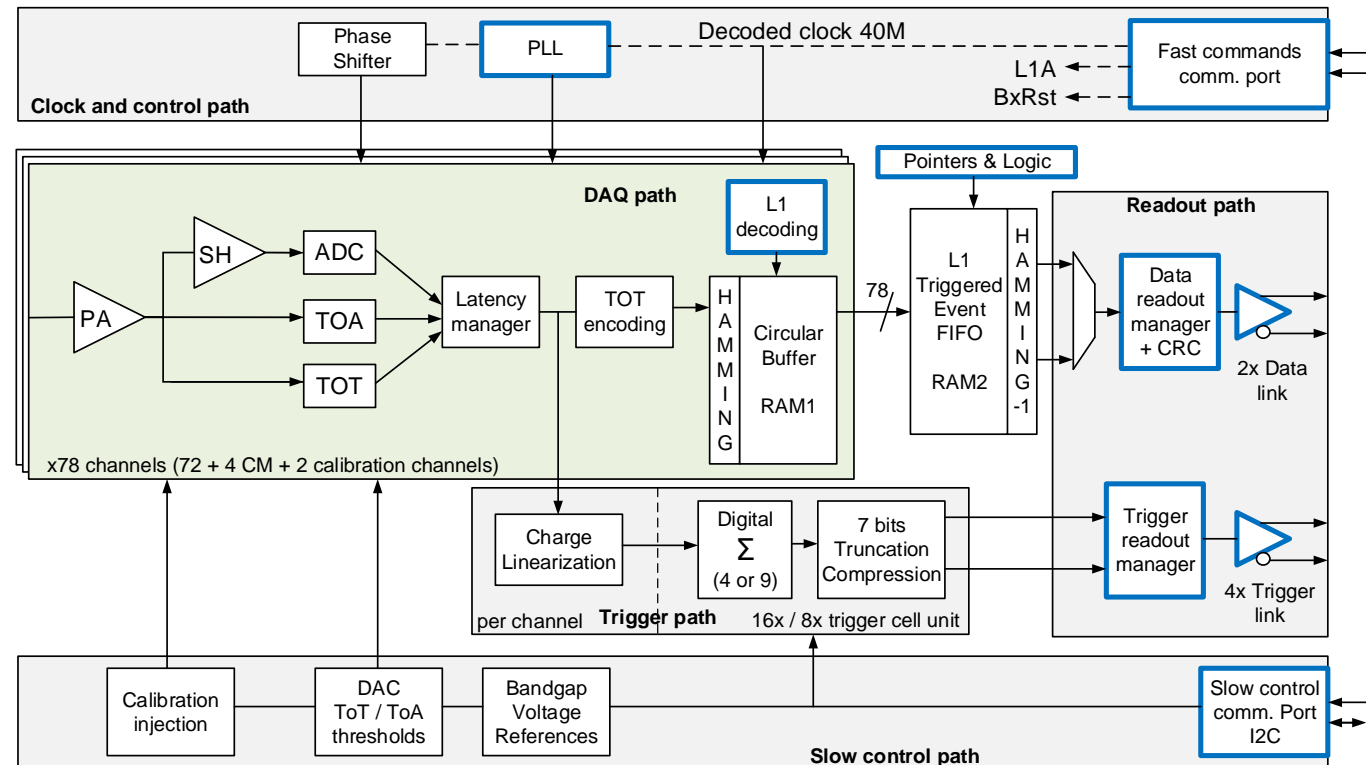
- 1.2V power supply for the very front-end
- Charge dynamic range: **0.2 fC to 10 pC**
- Timing accuracy **< 100ps** for pulses above **3 MIPs (12fC)** for a  $C_{det} = 65pF$
- Compensation of the leakage current up to **50 $\mu$ A**
- Radiation resistance up to **200 MRad**

\*Friday talk by **Fakhri Alam Khan**



**HGCROC3:**  
High density

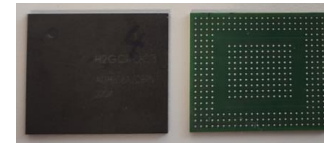
[4]



  : Triplicated

## Requirements for H2GCROC (The SiPM version of the ASIC):

- 2.5 V power supply for the very front-end to cope with SiPM bias voltage
- Charge dynamic range : **160 fC to 320 pC**
- Timing accuracy **< 100ps** for pulses above **3 MIPs (4.5pC)** for a  $C_{det} = 100pF$
- Compensation of the leakage current up to **1mA**
- Radiation resistance up to **300 kRad**
- **Input DAC** to tune the input voltage in order to compensate for breakdown voltage fluctuation

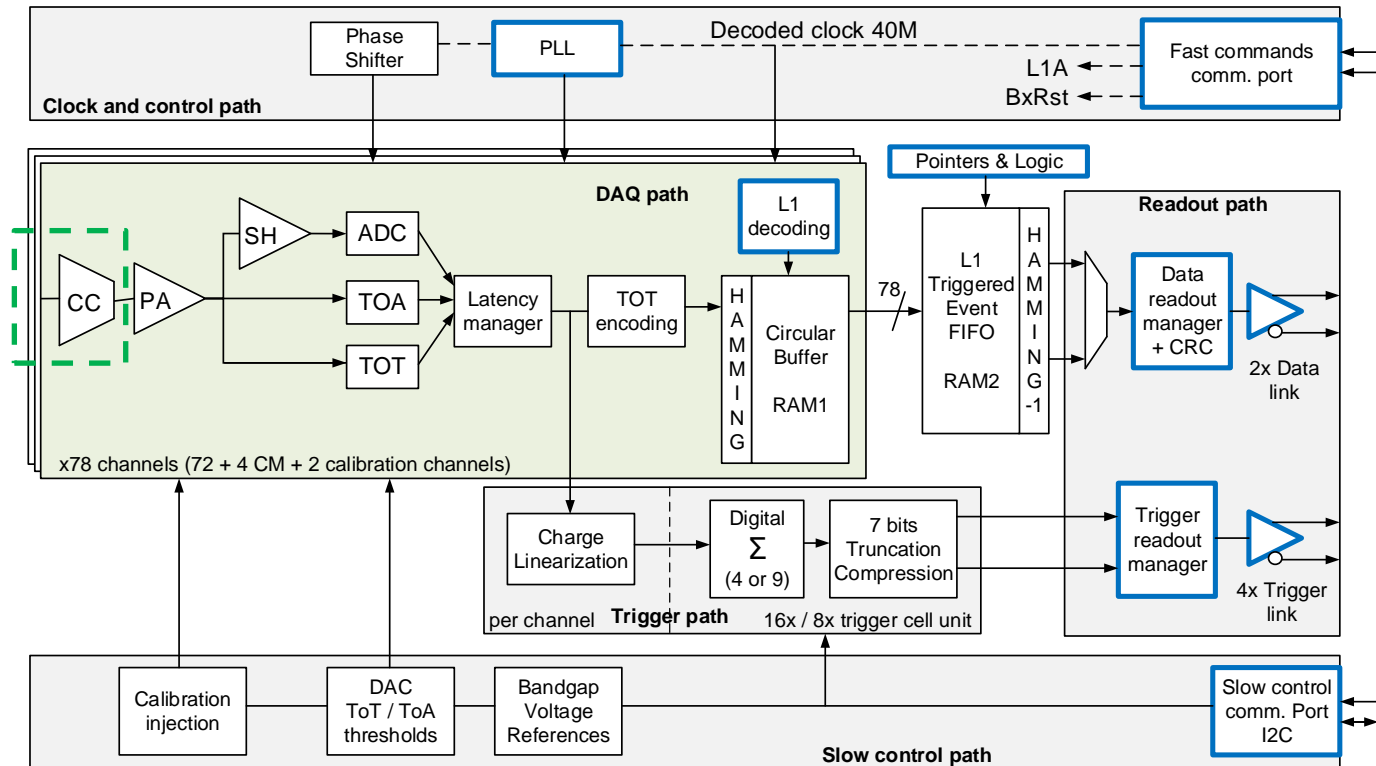


**H2GCROC3:**  
Low density

**Current Conveyor**  
based on KLAUS  
chip from Heidelberg  
UNI. [6]

Attenuates the  
current at the input  
with 4 bits.

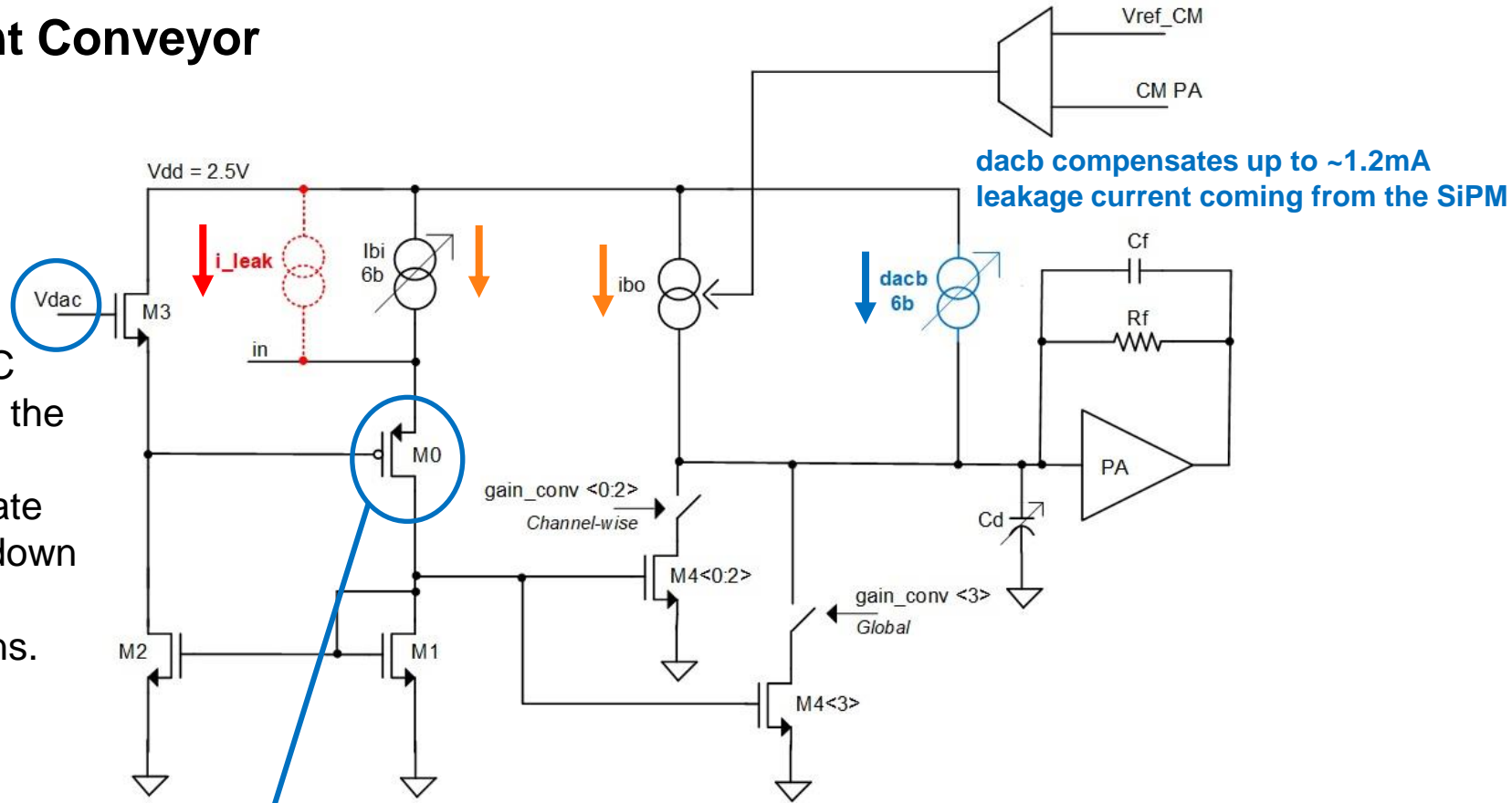
**CC gain:**  
**0.025 to 0.375**  
(step 0.025)



: Triplicated

## Current Conveyor

Tuning DC voltage at the input to compensate for breakdown voltage fluctuations.



dacb compensates up to ~1.2mA leakage current coming from the SiPM

Current mode feedback to increase the gm

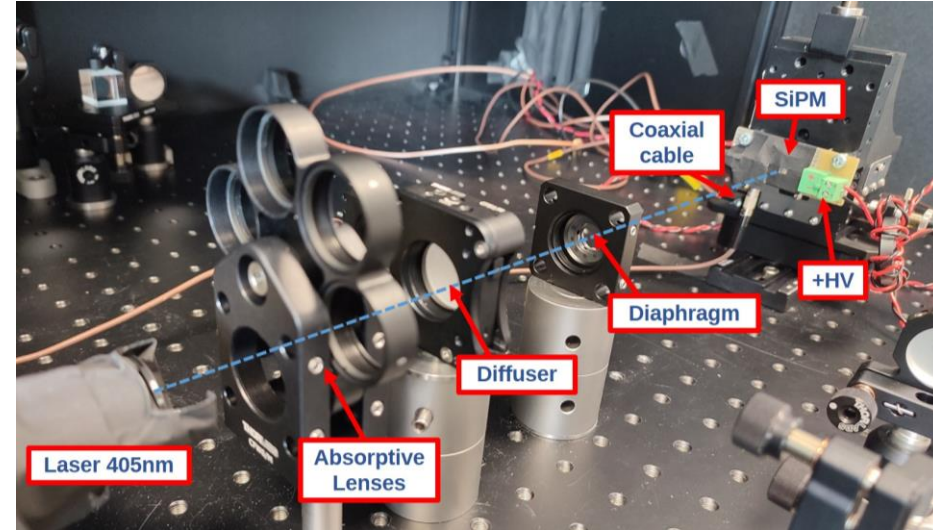
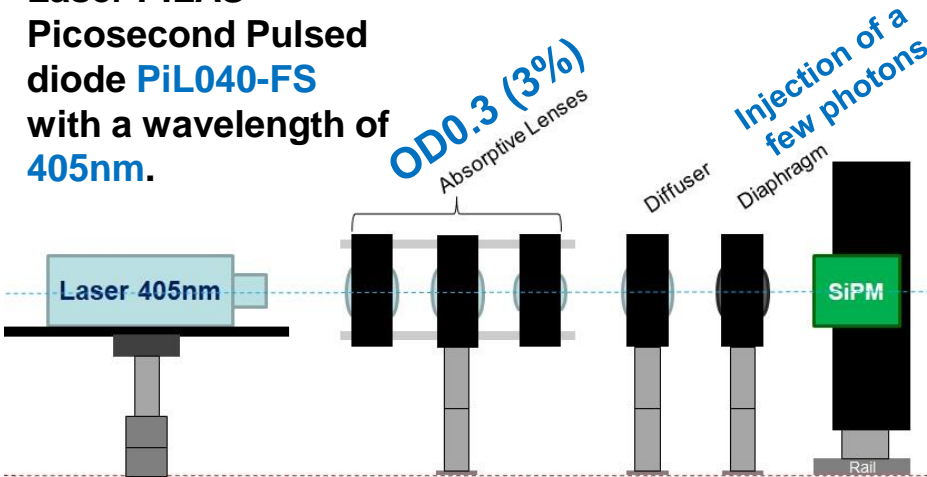
CC gain = 0.025 to 0.375 (step 0.025)

[4]

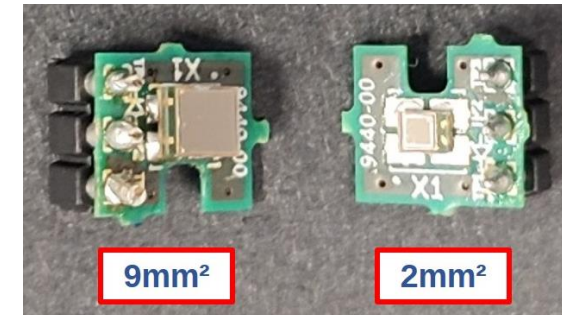
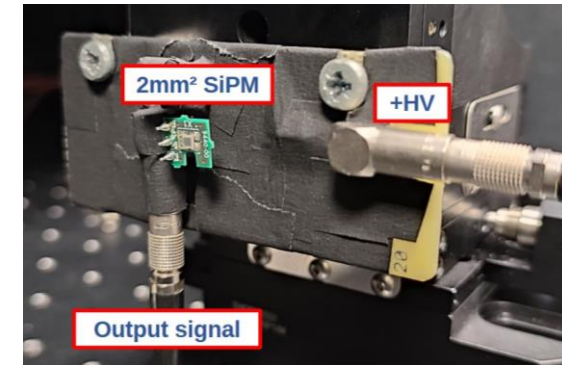
- **2 typical gains**

- High gain (Calibration mode): **4-7 fC/ADC gain, 9-20 fC noise**
- Low gain (Physics mode): **16-23 fC/ADC gain, 20-35 fC noise**

**Laser PILAS**  
**Picosecond Pulsed**  
**diode PiL040-FS**  
**with a wavelength of**  
**405nm.**

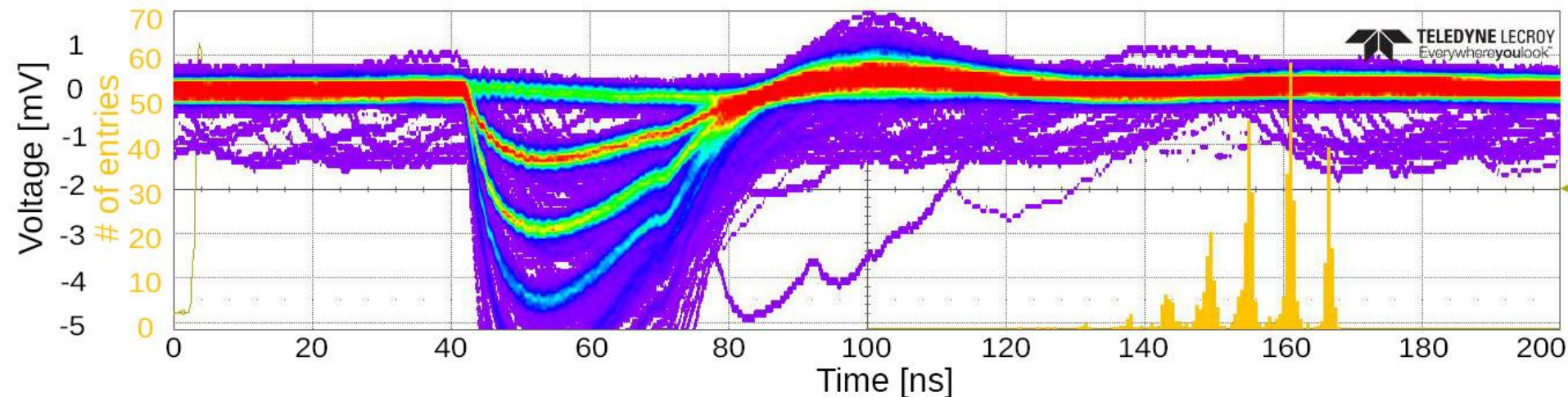


- **SiPM sizes in HGCal** were considered to be **2mm<sup>2</sup>** and **4mm<sup>2</sup>**.
- Radiation damage to scintillators and increased noise in irradiated SiPMs have led to use **9mm<sup>2</sup>** SiPMs in certain regions.
- **Two SiPMs tested:**
  - SiPM S14160-1315PS with an effective photosensitive area of **2mm<sup>2</sup>** and a pixel pitch of 15 $\mu$ . [7]
  - S16713 Hamamatsu pre-series SiPM with an effective photosensitive area of **9mm<sup>2</sup>** and a pixel pitch of 15 $\mu$ .



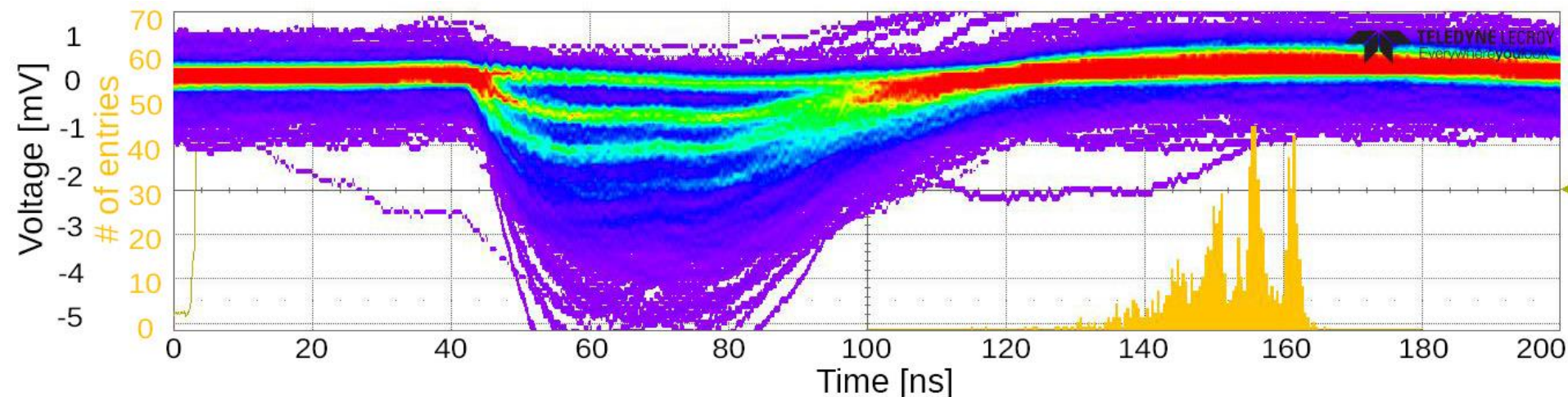


## SiPM 2mm<sup>2</sup>:



- Clear separation of all photon peaks after factor 5 amplification.

## SiPM 9mm<sup>2</sup>:



- Larger noise after factor 5 amplification. Slower rising and falling times
- Hard to see photon separation after the third photon.

Large area SiPM have larger  $C_G$  capacitance and larger number of pixels that both increase the total capacitance of the detector ( $C_{det}$ ).

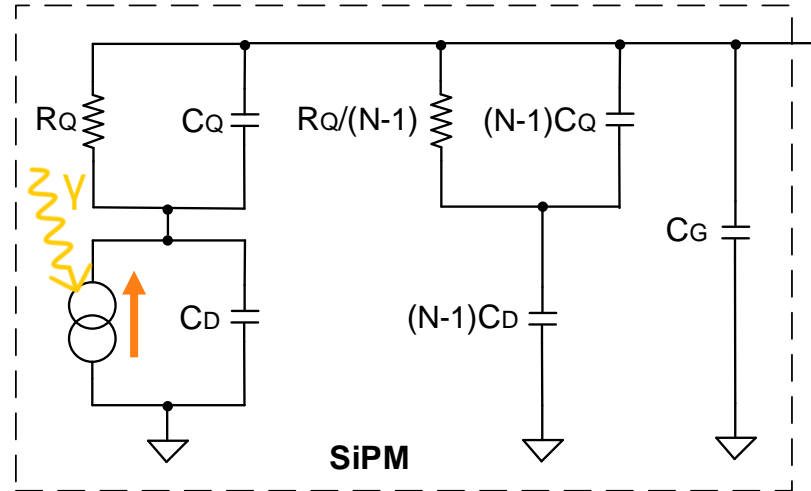
The SiPM capacitance is dominated by  $C_G$  value. However, to have an equivalent capacitance an extra margin need to be added to consider the capacitance of each pixel.

- Equivalent detector capacitance of SiPMs:

$$\begin{aligned}
 2\text{mm}^2: & \quad C_{det} = 120\text{pF} \\
 4\text{mm}^2: & \quad C_{det} = 270\text{pF} \\
 9\text{mm}^2: & \quad C_{det} = 560\text{pF}
 \end{aligned}$$

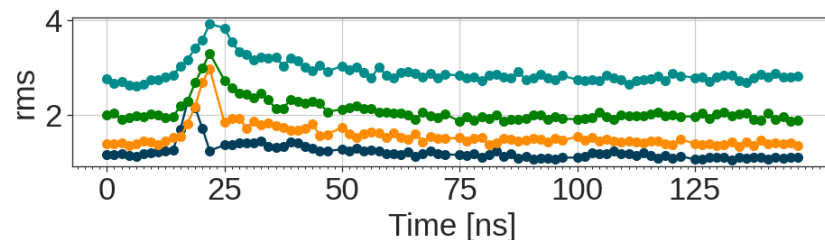
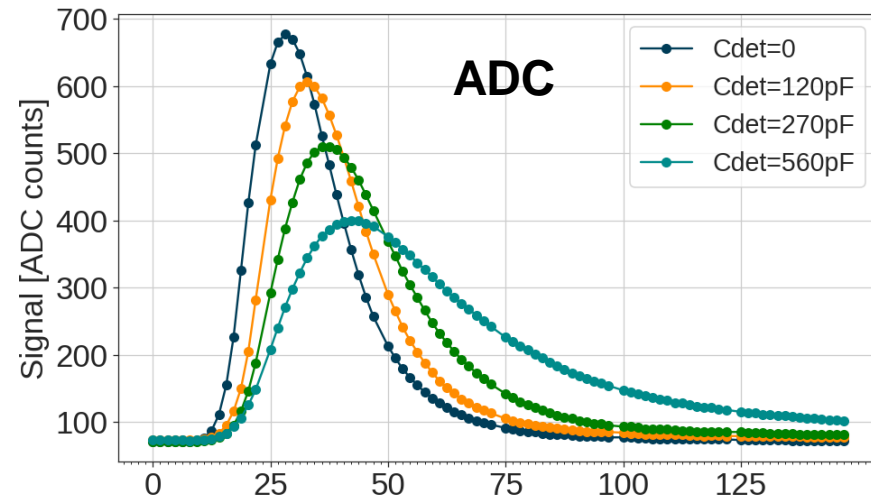
The internal injection of the ASIC can be configured to inject **2.47pC** using an internal DAC and a 3pF capacitor.

The impact of different external capacitors connected to 4 different channels are shown to simulate the detector response.

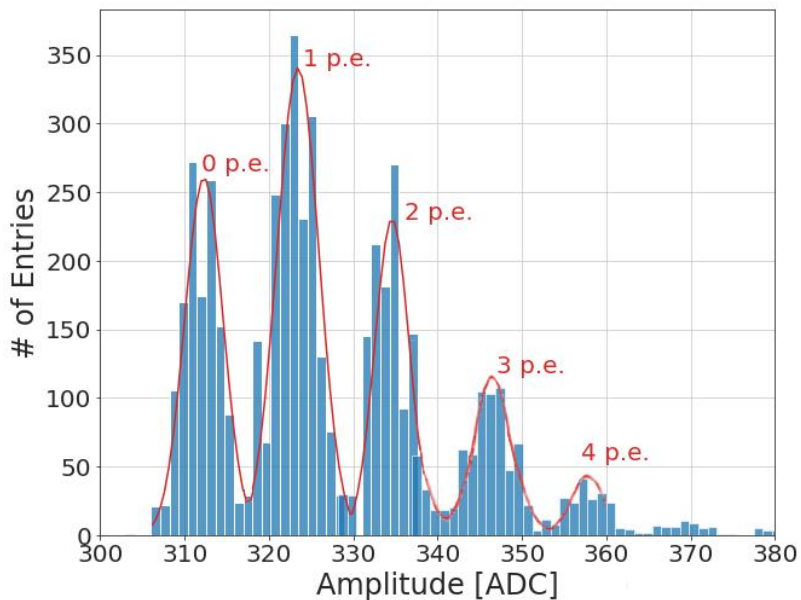


$N$  = # of micro-cells  
 $C_D$  = Capacitance of photodiode in the micro-cell  
 $R_Q$  = Quenching resistance  
 $C_Q$  = Parasitic capacitance  
 $C_G$  = Total parasitic capacitance

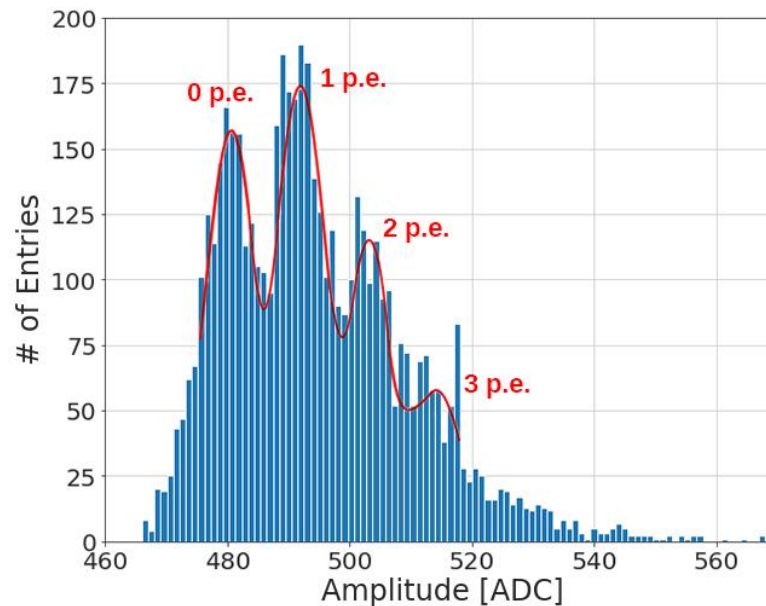
[14]



- **2mm<sup>2</sup>:**



- **9mm<sup>2</sup>:**

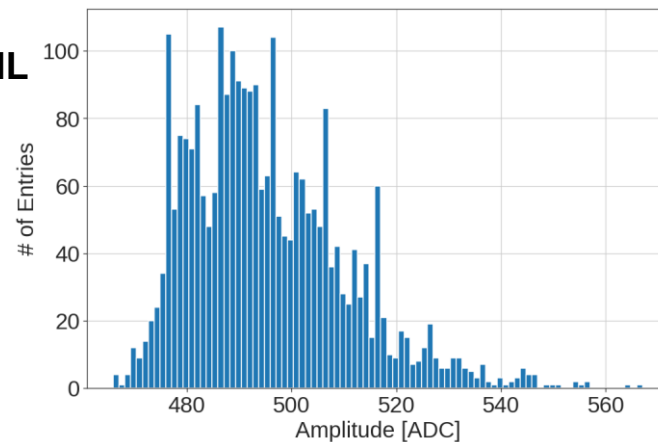


**\*Extra step for 9mm<sup>2</sup> SiPM calibration:**

The large  $C_{det}$  of the 9mm<sup>2</sup> SiPM produce an increment of DNL and make it harder to see the photon separation.

The DNL can be mitigated taking data with different pedestal levels using the ASIC to move the pedestals (*Trim\_inv* parameter). SPS is clearer after aligning the data.

**Without DNL correction:**



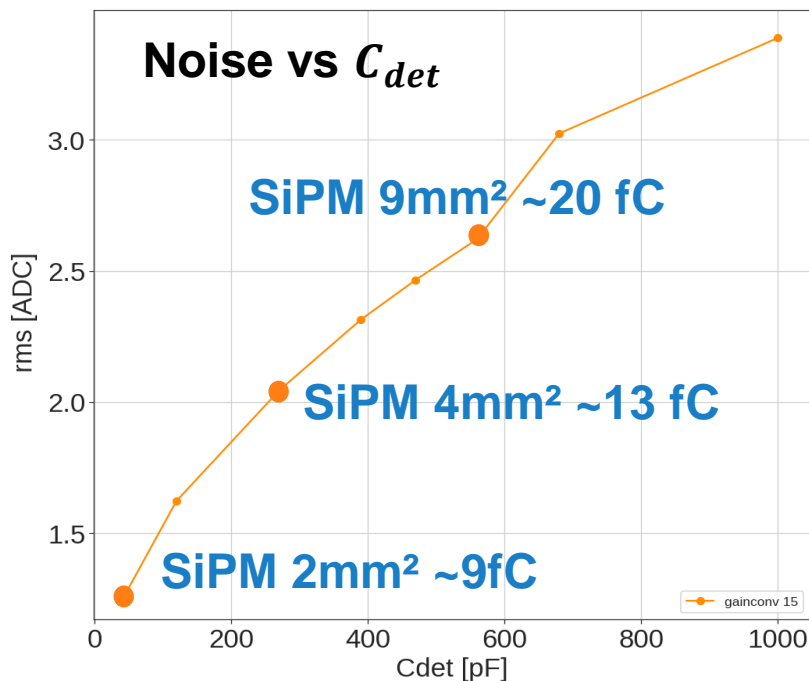
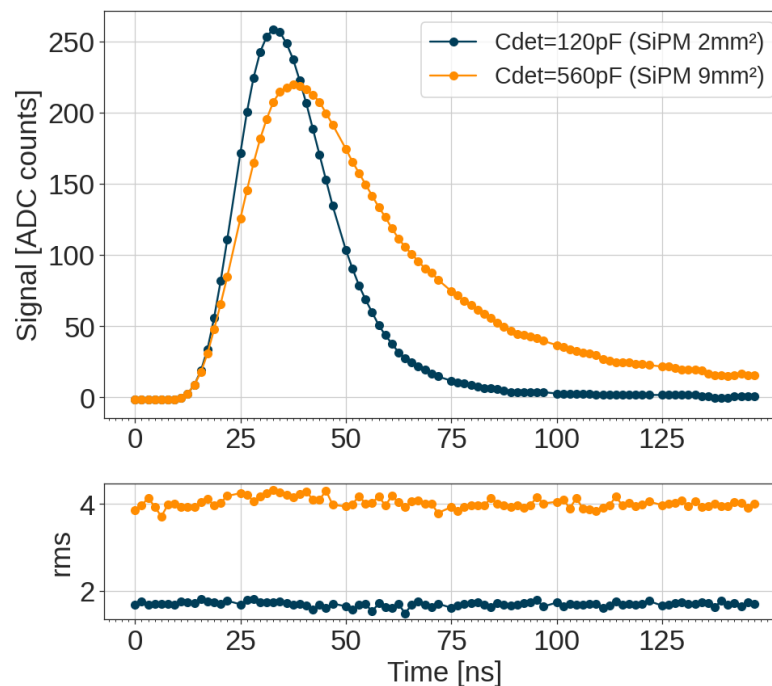
Also a different configuration of the ASIC is necessary to increase the SNR.

## 2mm<sup>2</sup>:

- CC gain attenuation = **0.3**
- $R_f = 16.6 \text{ k}\Omega$
- $C_{f\_total} = 600 \text{ fF} (C_f + C_{f\_comp})$

## 9mm<sup>2</sup>:

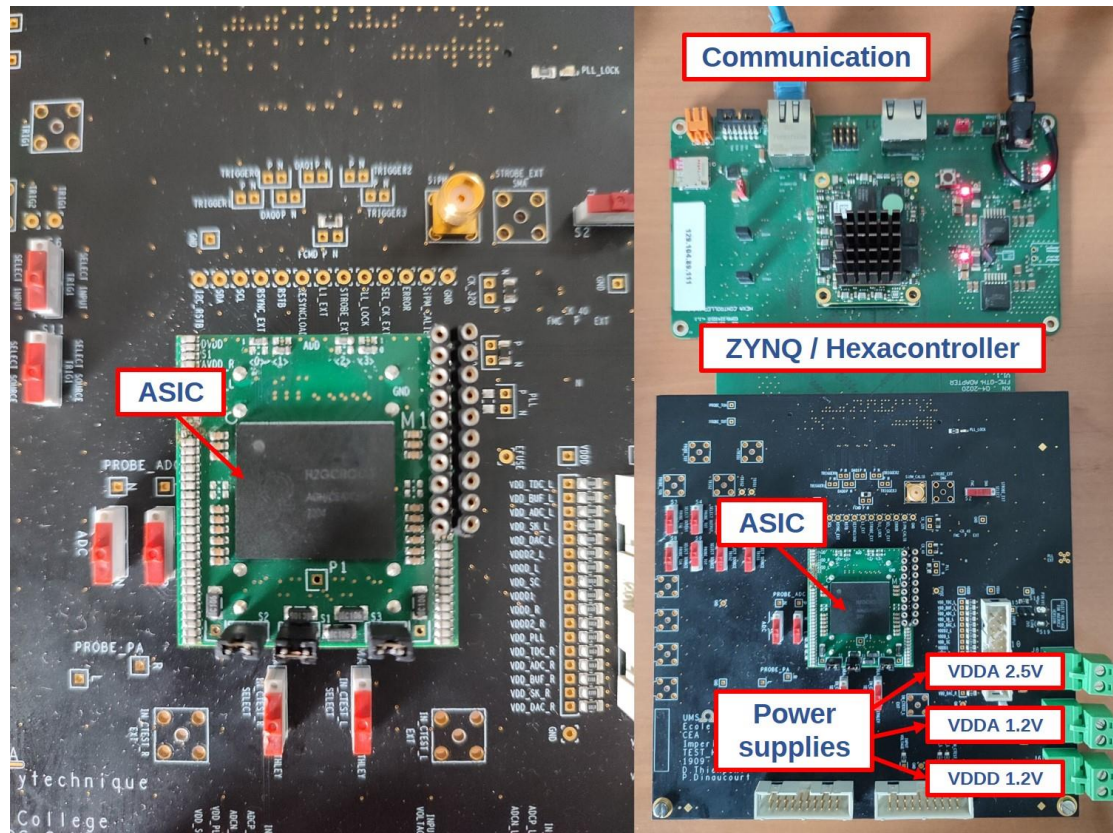
- CC gain attenuation = **0.375**
- $R_f = 16.6 \text{ k}\Omega$
- $C_{f\_total} = 300 \text{ fF}$  (To make the pulse shorter)



\*Noise measured with the same configuration parameters for all  $C_{det}$ .

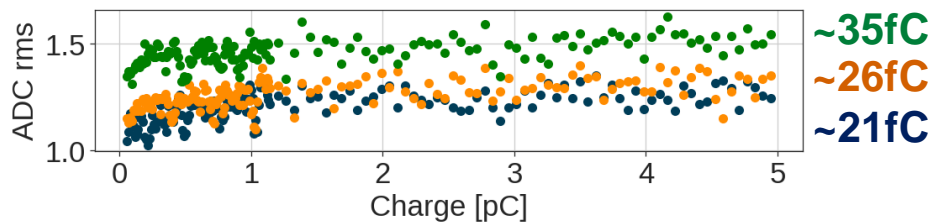
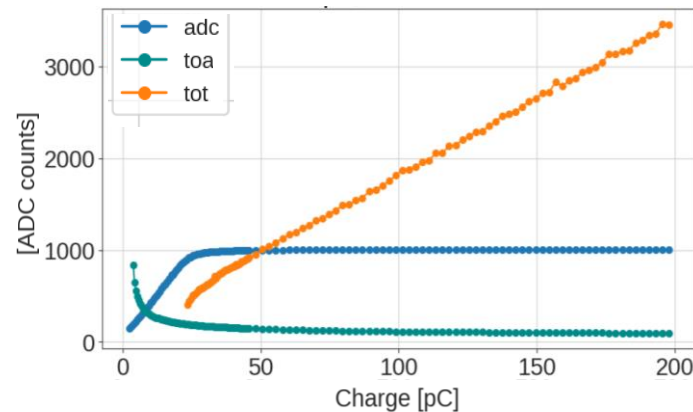
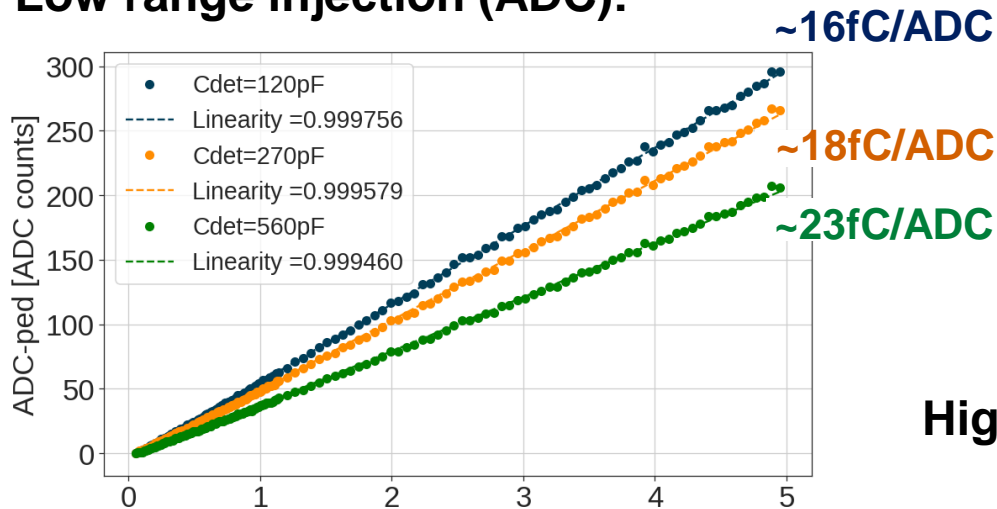
- The increment in noise is due to the detector capacitance of the SiPM.
- SNR can be improved with the gain configuration.

- The ASIC has an internal 12 bit DAC that can inject up to 1.7V.
  - Each channel has a 3pF capacitor available at the input.
  - **Low range injection:** Uses just one 3pF capacitor in the selected channel. Charge injection up to **~5pC**
  - **High range injection:** It uses every 3pF capacitor of each channel in parallel and uses the sum of all capacitances (117pF) to convert the DAC voltage to a charge. Charge injection up to **~195pC**

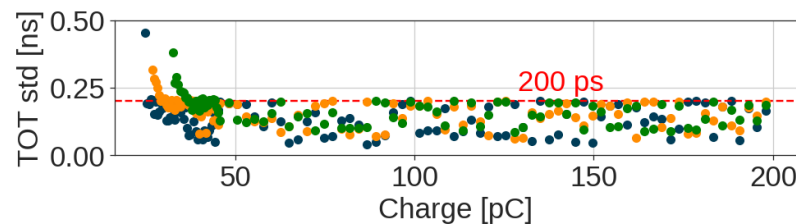
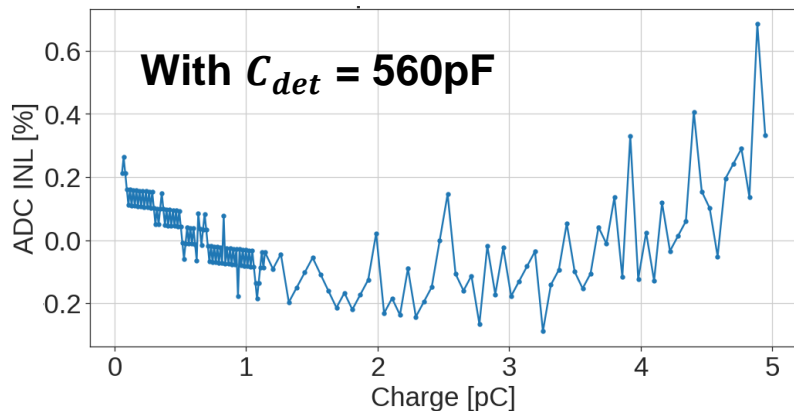
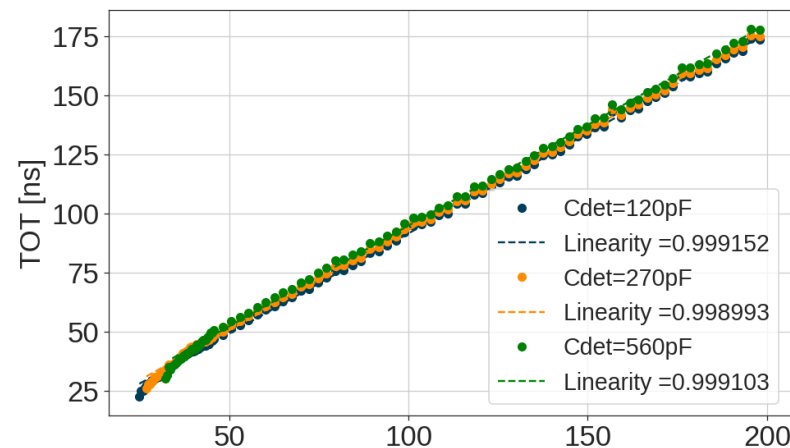


- ~ 60 fC minimum detectable charge efficiently, up to 320pC

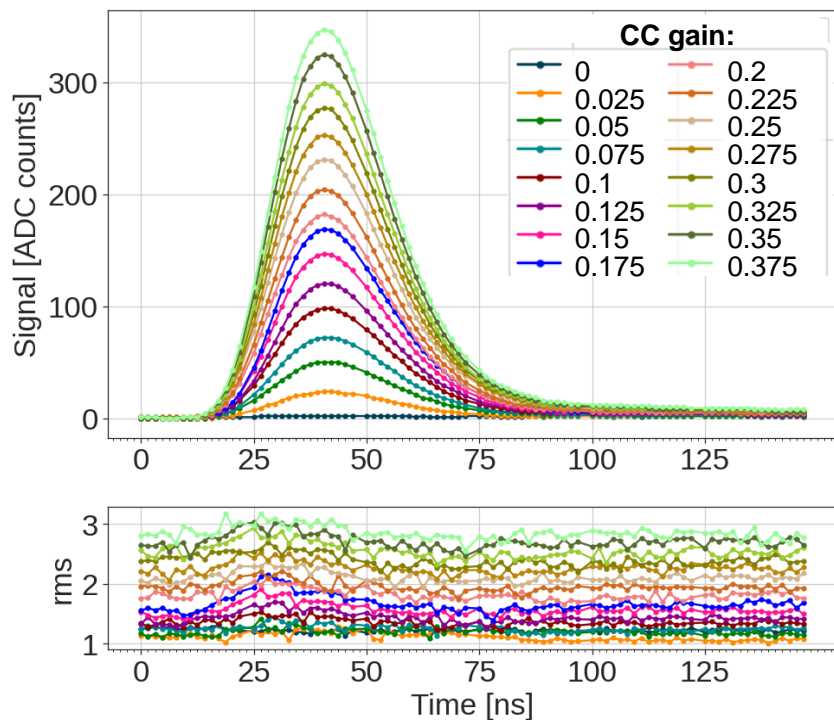
## Low range injection (ADC):



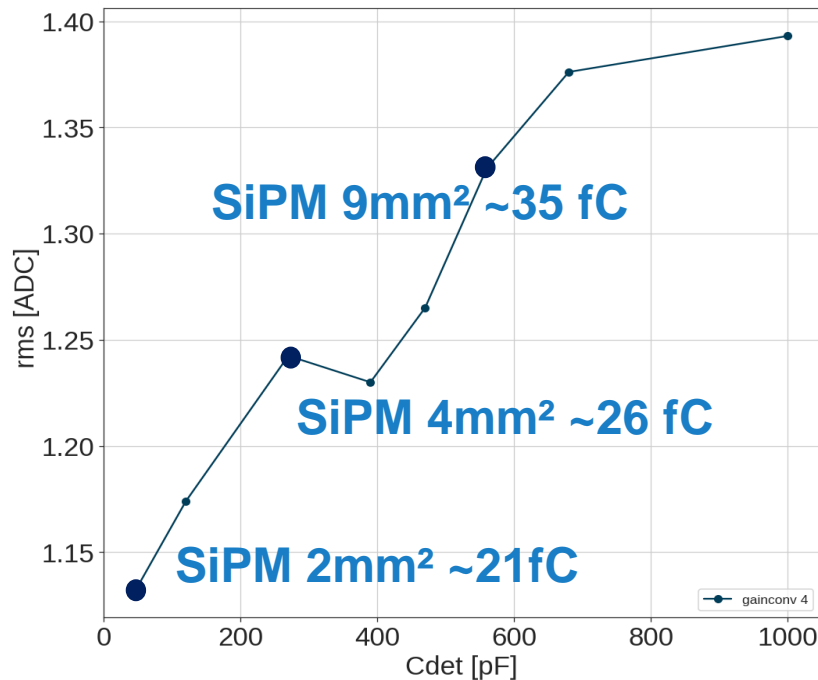
## High range injection (TOT):



## CC gain scan:



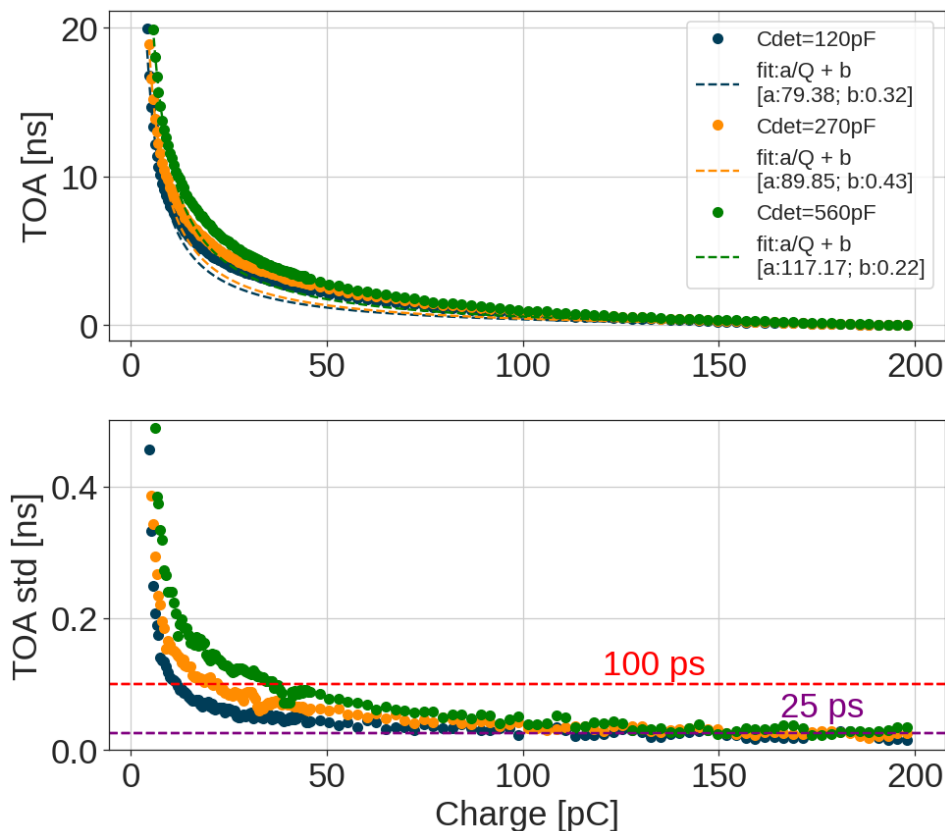
## Noise vs $C_{det}$ :



- The CC gain has good performance in linearity.
- The increment in noise is due to the gain configuration and the detector capacitance of the SiPM.

\* May be necessary to have a configuration file for each SiPM. Both the calibration mode and physics modes.

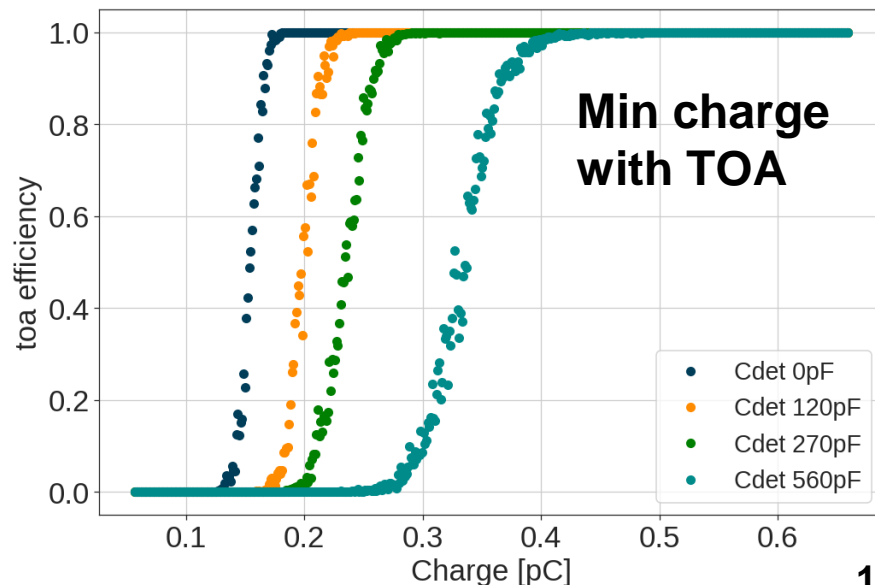
## TOA:



- The increase in noise due to larger  $C_{det}$  shifts the minimum charge associated with TOA data.
- The thresholds can be adjusted channel-wise for a uniform performance.

## Effect of $C_{det}$ on TOA:

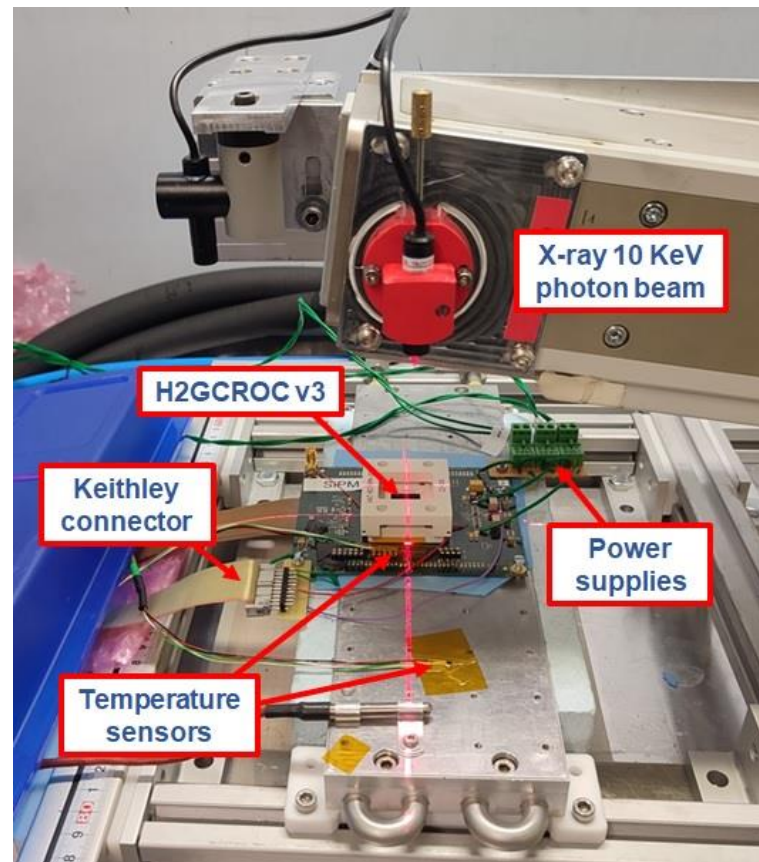
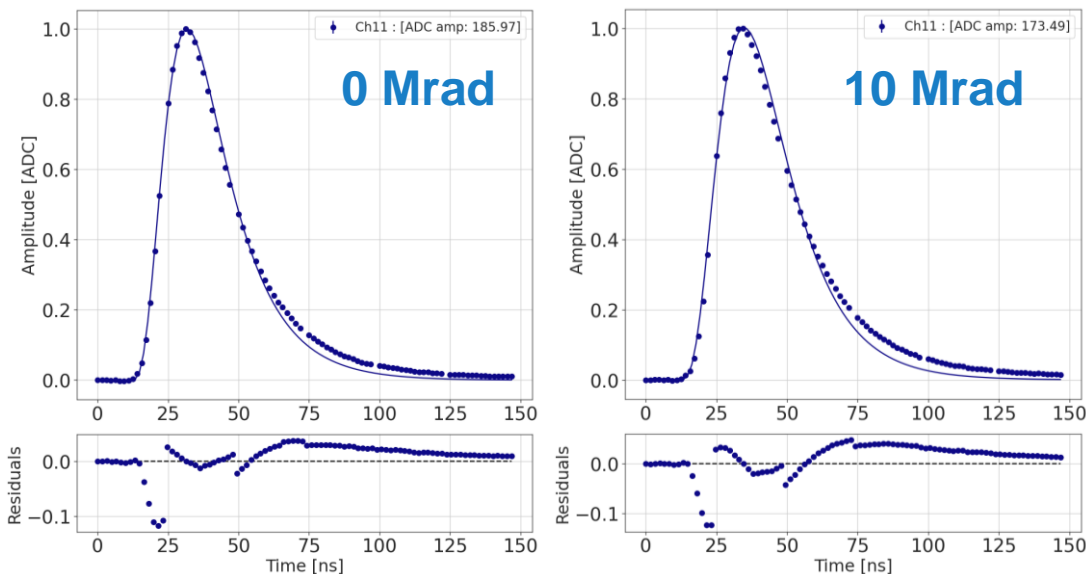
- Larger  $C_{det}$  produce larger time walk due to the duration of the signal.
- Increasing  $C_{det}$  delayed the achievement of a 100ps resolution in charge injection.





- Power consumption, ADC & TDC performance, noise, links stability, etc. tested during irradiation
- **TID irradiation tests in both ASIC versions.** [8,9,10,11]
- **Heavy ion and Proton irradiation in the Si version of the ASIC** [12,13]
  - Increase on triplicated parts for HGCROC3b

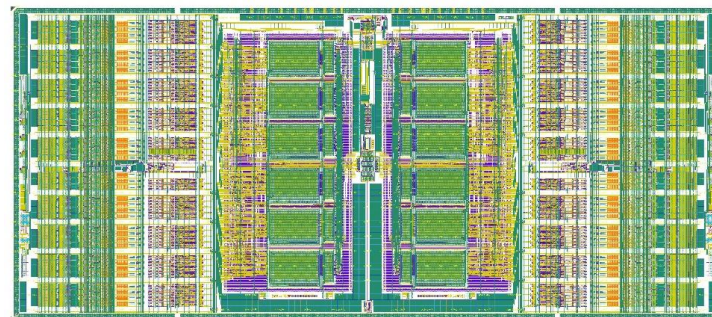
## Stability of ADC measurements after 10Mrad:



- **H2GCROCv3** has proven to be **radiation tolerant up to 10 Mrad** at **-5°C** with good ADC, TDC and PLL measurements.

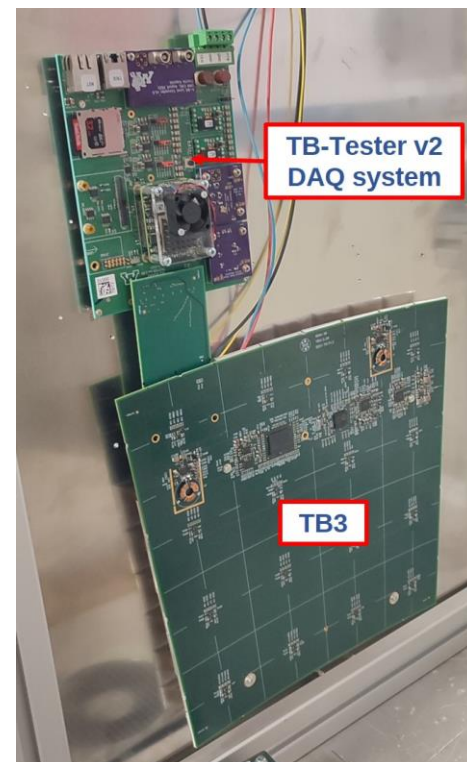
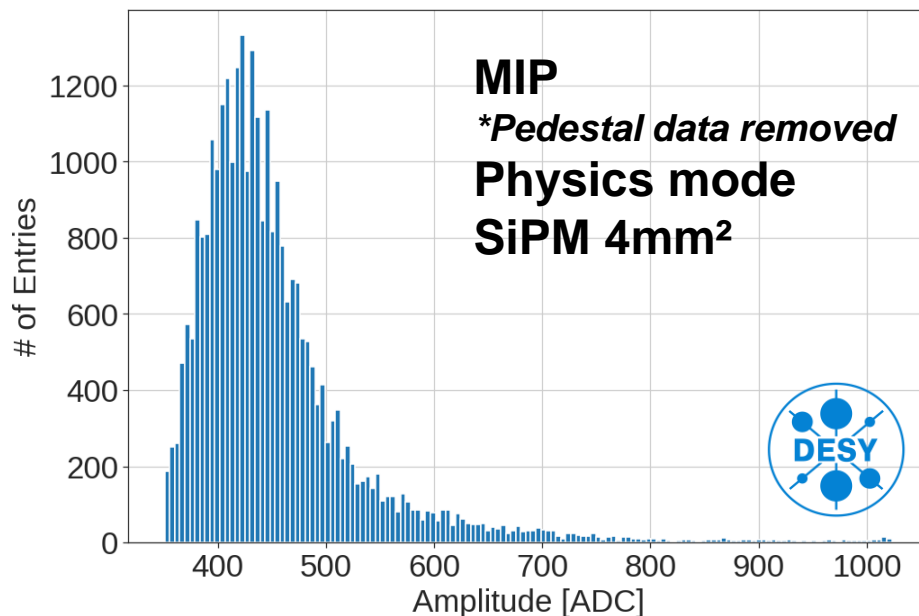
- H2GCROC3 is robust enough to be calibrated for the different SiPM of HGCal
- The configuration of the ASIC needs to be carefully selected to adapt gain, linearity, time walk and charge range.
- ASIC tested at beam and TID campaigns.
- Minor corrections are expected for H2GCROC3b.

## H2GCROC3 Layout:



### Beam data:

\*Energy: 3GeV  
64ch Tileboard  
fully equipped  
with 4mm<sup>2</sup> SiPM



\*The measurements leading to these results have been performed at the Test Beam Facility at DESY Hamburg (Germany), a member of the Helmholtz Association (HGF).

Thank you for your attention



## Overall chip divided in two symmetrical parts

- **1 half is made of:**
  - 39 channels: 18 ch, CM0, Calib, CM1, 18 ch
  - Bandgap, voltage reference close to the edge
  - Bias, ADC reference, Master TDC in the middle
  - Main digital block and 3 differential outputs (2x Trigger, 1x Data)

## Two data flows

- **DAQ path**
  - 512 depth DRAM (CERN), circular buffer
  - Store the ADC, TOT and TOA data
  - 2 DAQ 1.28 Gbps links
- **Trigger path**
  - Sum of 4 (9) channels, linearization, compression over 7 bits
  - 4 Trigger 1.28 Gbps links

## Control

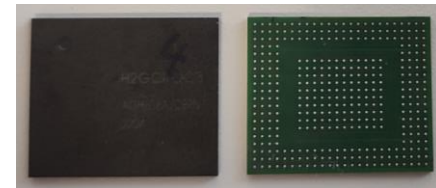
- **Fast commands**
  - 320 MHz clock and 320 MHz commands
  - A 40 MHz extracted, 5 implemented fast commands
- **I2C protocol for slow control**

## Ancillary blocks

- Bandgap (CERN)
- 10-bits DAC for reference setting
- 11-bits Calibration DAC for characterization and calibration
- PLL (IRFU)
- Adjustable phase for mixed domain

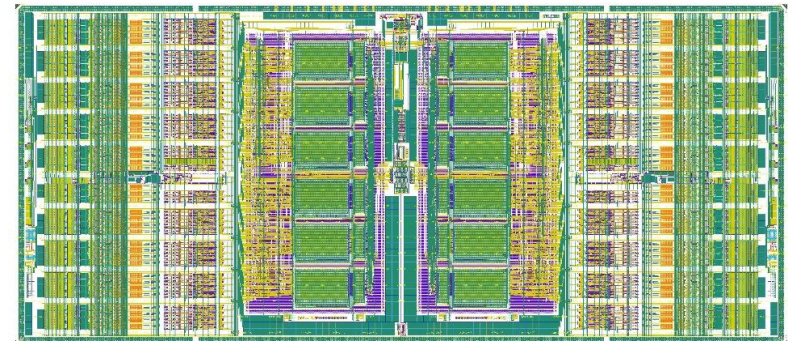


**HGCROC3**  
High density

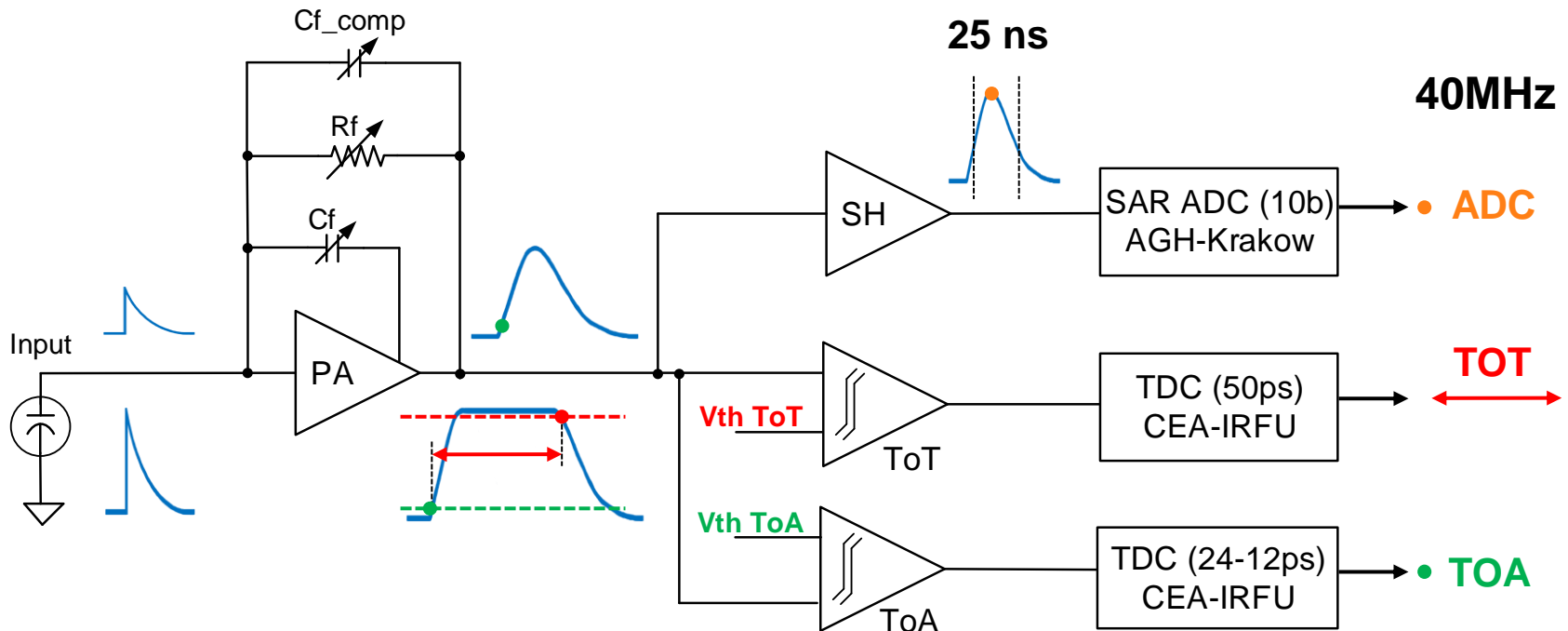
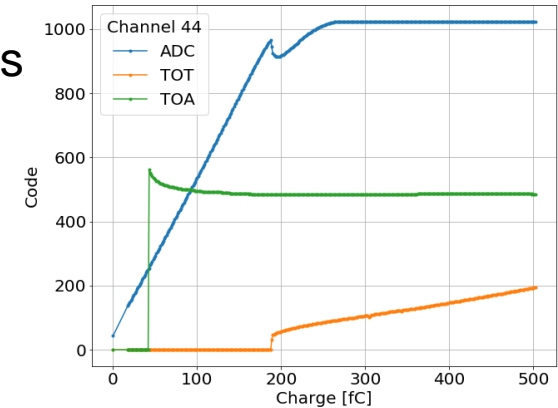


**H2GCROC3**  
Low density

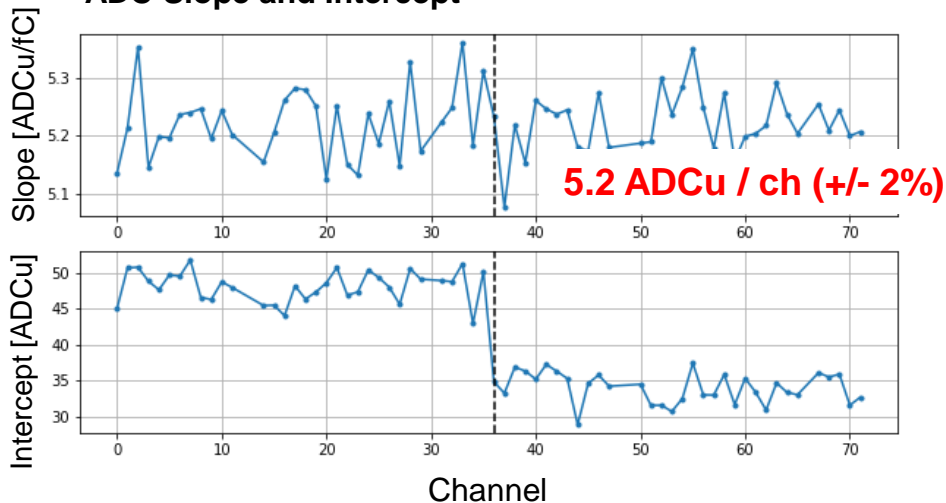
## HGCROC3 Layout:



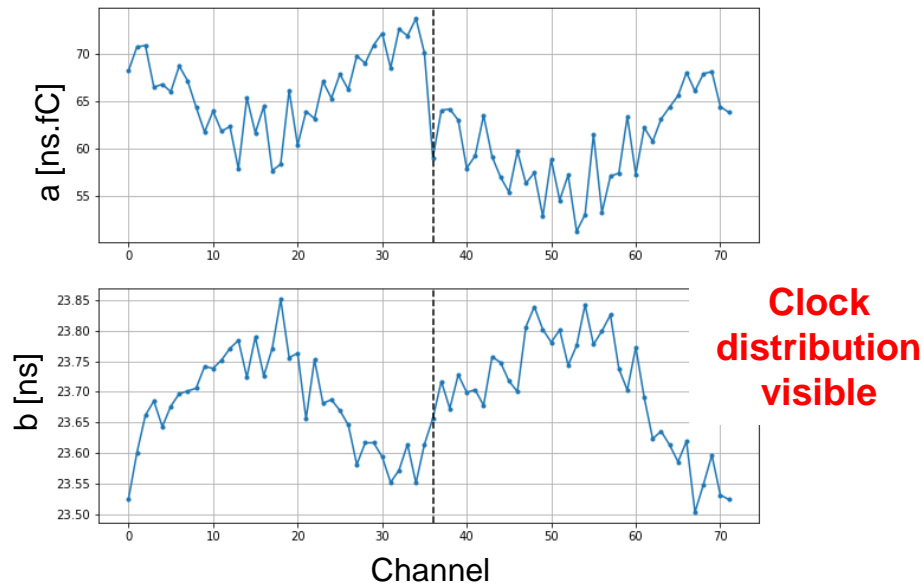
- **Calibration pulser**, 0.5pF and 10 pF calibration cap.
- **Preamp** : adjustable gains for 80, 160 and 320 fC ranges
- **Tunable TOT** over 5 bits
- **Sallen Key shaper RC4**,  $t_p < 25$  ns, tunable ( $\sim 20\%$ ) with 2 bits,  $BX+1/BX < 0.2$
- Temperature stabilization to  $< 0.5$  mV/K
- **10 bit ADC from Krakow AGH**
- **TOT and TOA TDCs from CEA-IRFU**



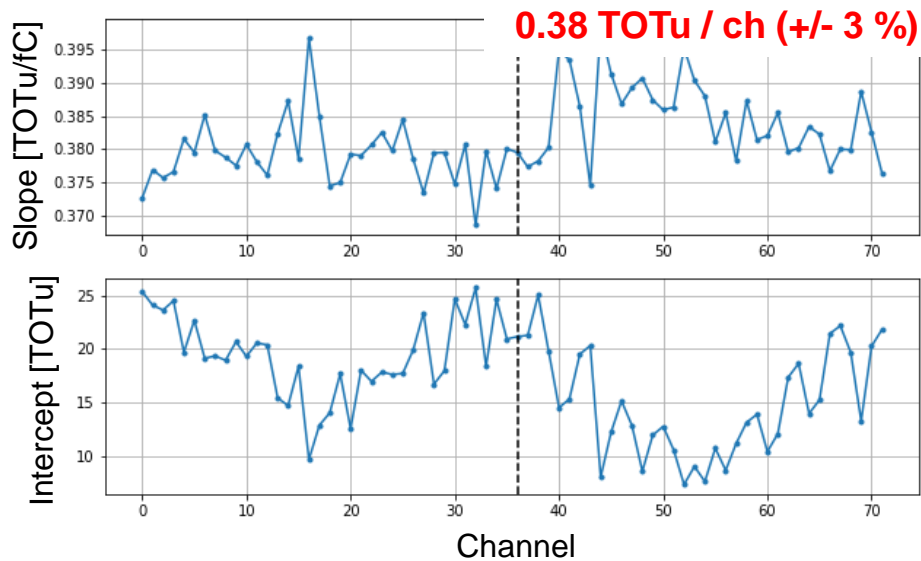
### ADC Slope and Intercept



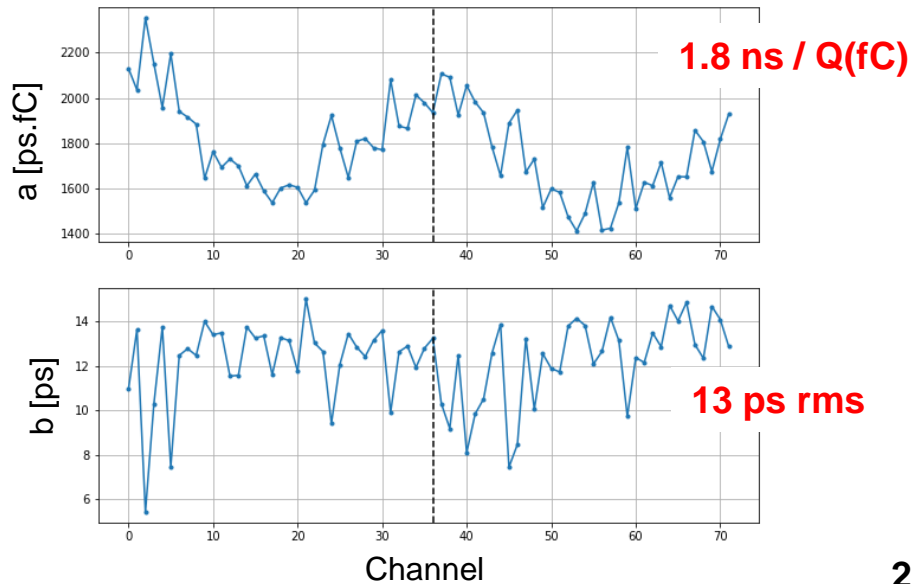
### TOA Time Walk. a & b parameters of the $a/Q + b$ fit



### TOT Slope and Intercept

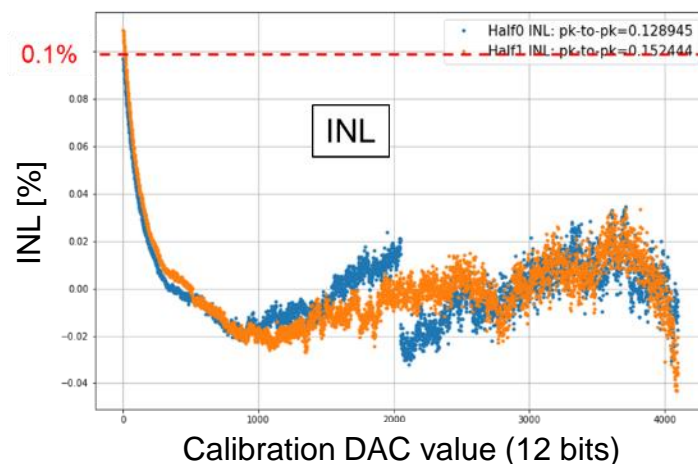


### TOA Jitter. a & b parameters of the $\sqrt{(a/Q)^2 + b^2}$ fit



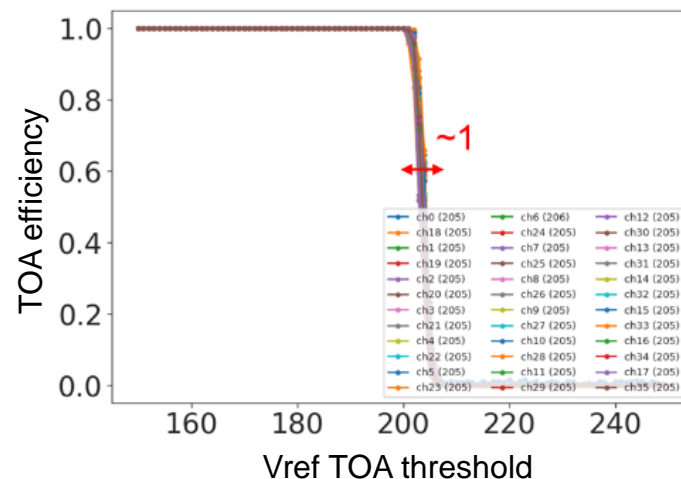
- **12 bits calibration DAC**
  - ~ 2-3 mV offset due to leakage current (1 – 1.5 fC)
  - < 0.1 % linearity, temperature sensitivity: 60 ppm/K, stable after 350 Mrad
- **Four 10-bit DACs** to set pedestals, TOA & TOT thresholds + **3 channel-wise 6-bit DACs** to reduce dispersion per channel
  - Pedestals: ~ 1 ADC counts dispersion after trimming
  - TOA & TOT thresholds: 1-2 DAC counts after trimming
- 8-bit input DAC to compensate for the **leakage current up to 50  $\mu$ A**
  - Additional noise as expected from simulation

## Calibration DAC:

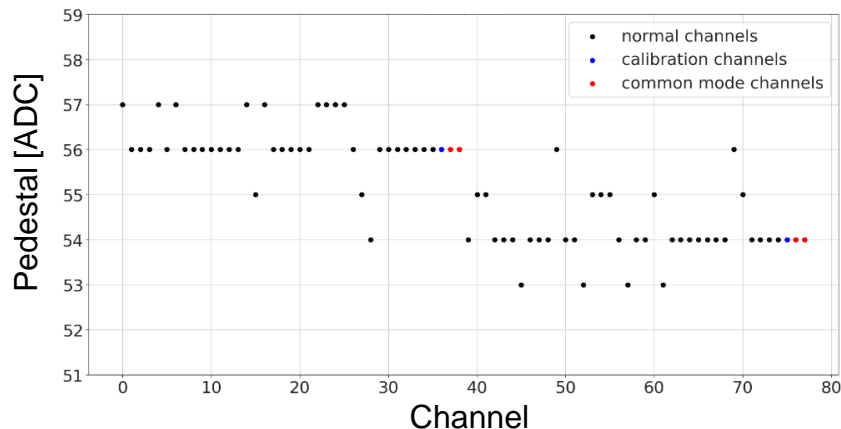


## Trimmed TOA thresholds:

10-bit global threshold scan

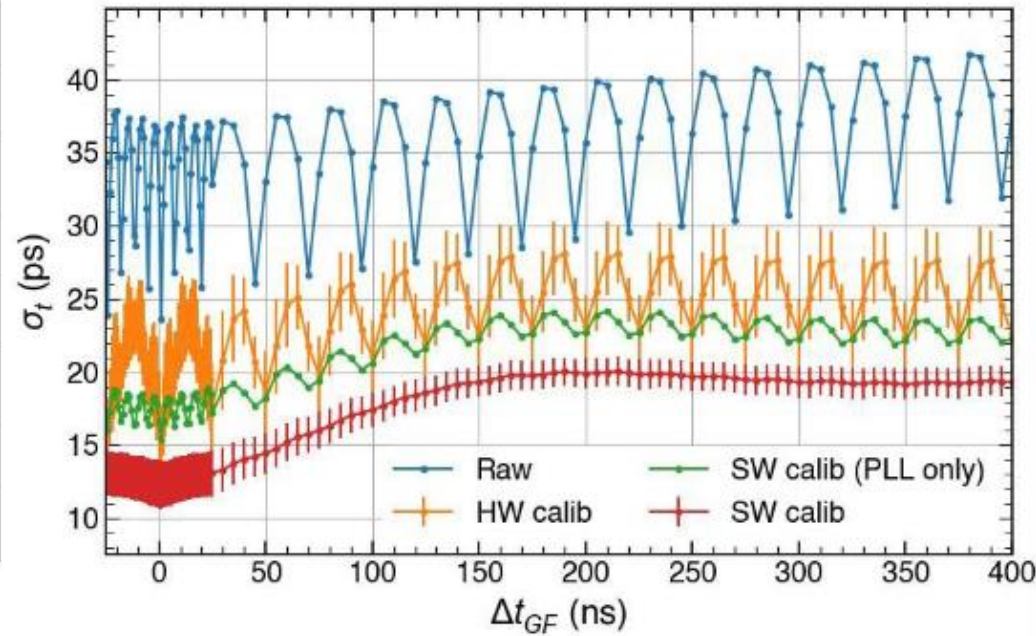
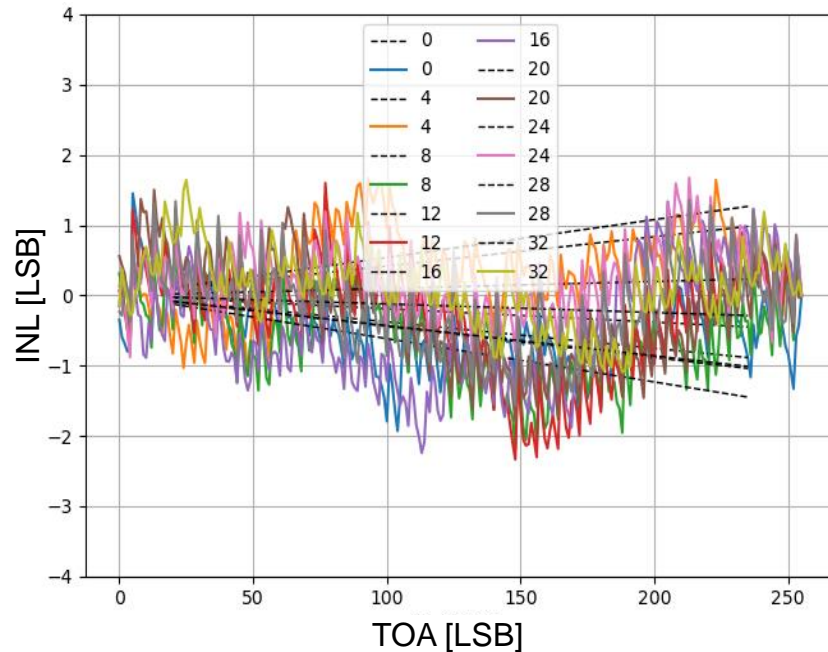


## Trimmed pedestals:





- I2C parameters to tune master and channel-wise DLLs
- Parameters can be optimized thank to the on-chip asynchronous clock generator (ACG) by minimizing the INL.



## TDC calibration in 2 steps:

- Master DLL tuning
- Individual channel DLL tuning

**After Calibration: INL < ± 2 LSBs, < 16 ps resolution**

## Resolution of 2 uncorrelated chips given by resolution at large T-delays

- Before calibration (blue): ~ 40 ps resolution
- After calibration (orange): < 30 ps resolution
- (After software correction (cancel FPGA clock jitter): **< 20 ps resolution**)

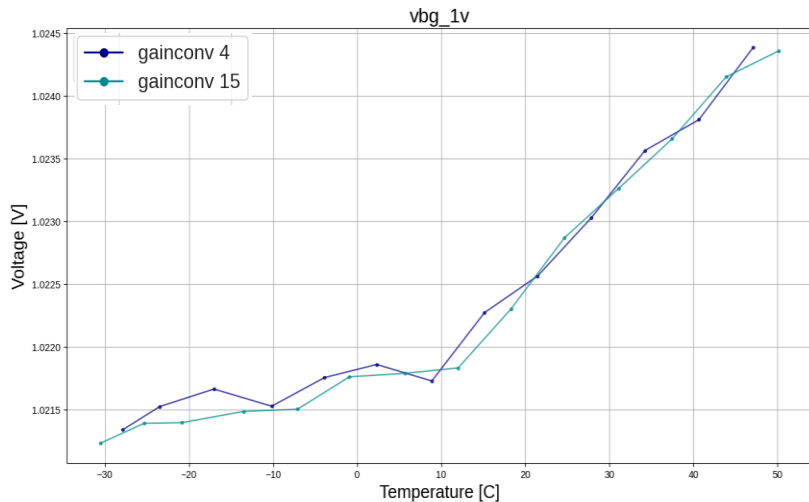
- Only tested in **HGCROC Si version** for both Protons and Heavy ions.
- Test the radiation damage induced by a single particle to electronic devices and non-cumulative. It can cause a failure at any moment since the beginning of operation.
- **Three types:**
  - Single Event Upset (**SEU**): bit flip (0 -> 1 or 1 -> 0).
  - Single Event Transient (**SET**): bit shift.
  - Single Event Latchup (**SEL**): permanent damage.

# errors	Counters	Trigger	CRC	Memory	Short SET	<b>Long SET</b>
<b>Heavy ions</b> [12]	0	1	2	3	24	<b>18</b>
<b>Protons</b> [13]	< 1	38	30	127	85	<b>190</b>

**1 link loss / 2.5 years (for each chip on average)**

- Very few errors in the not triplicated parts of Trigger and CRC.
- Very few errors in the memory, always detected by the hamming.
- Many errors in the not triplicated part (**PLL**).
  - **Increase in the triplication of the new version of PLL (Tested in EICROC).**

*\*Analysis by Elena Vernazza*



**Bandgap (Two slopes):**

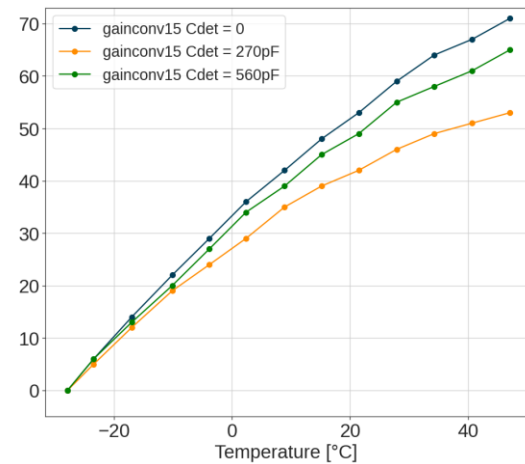
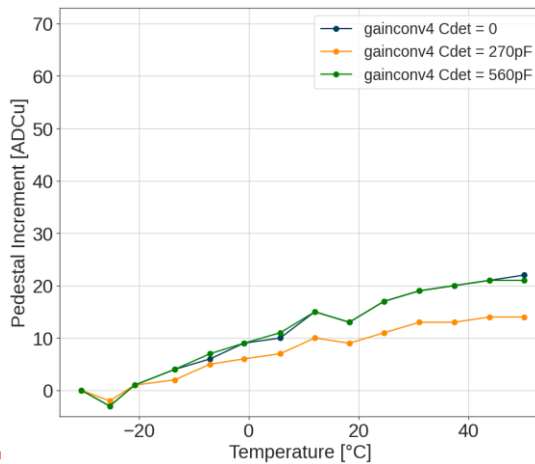
From  $-30^{\circ}\text{C}$  to  $10^{\circ}\text{C}$ :  $12.5 \mu\text{V} / ^{\circ}\text{C}$

From  $10^{\circ}\text{C}$  to  $50^{\circ}\text{C}$ :  $65 \mu\text{V} / ^{\circ}\text{C}$

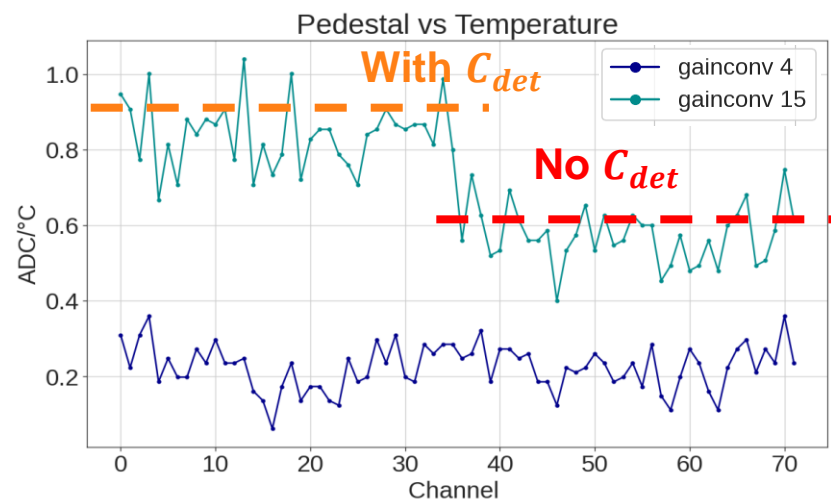
**Pedestals:**

Physics mode:  $+ 0.3 \text{ ADCu} / ^{\circ}\text{C}$

Calibration mode:  $+ 0.9 \text{ ADCu} / ^{\circ}\text{C}$



\*Noise : almost flat

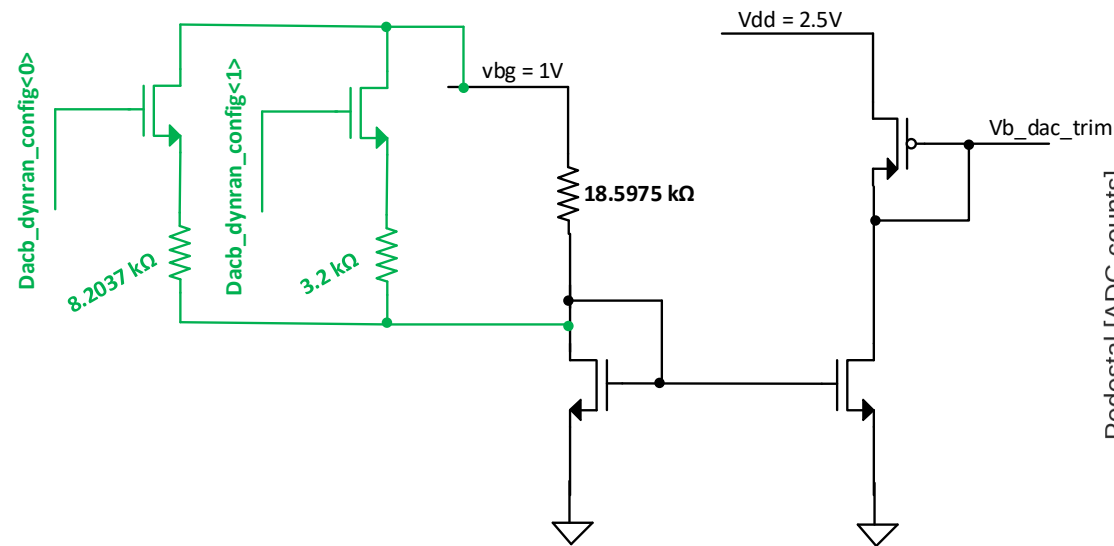


**Dacb\_dynran\_config (2 bits).** Extra resistors added to modify the current that controls the dynamic range of dacb.

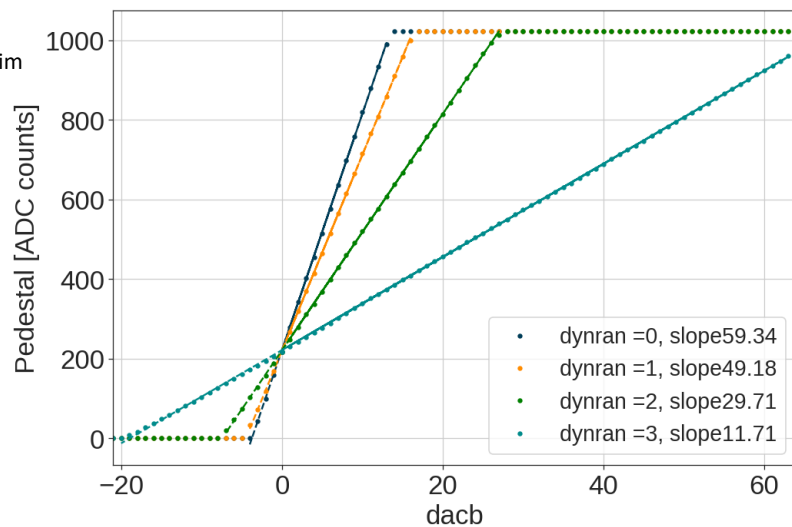
Dacb_dynran_config	Leakage current Correction range	Max dacb current	OUTPA pedestal step
0	0 to ~270 $\mu$ A	~21 $\mu$ A	~6.45mV
1	0 to ~660 $\mu$ A	~54 $\mu$ A	~16.4mV
2	0 to ~1.09 mA	~90 $\mu$ A	~27.2mV
3	0 to ~ <b>1.31 mA</b>	~109 $\mu$ A	~32.96mV

\*Optimum for  $I_{leak} = 1$  mA compensation with gainconv = 4

\*Extra correction for gainconv > 4



## H2GCROC3 measurements:



- **HGCROC3:** extrapolation for LD & HD modules (w/o LDO contribution)

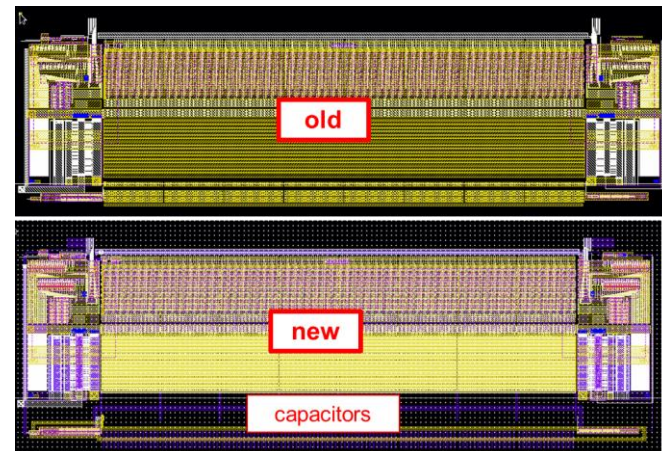
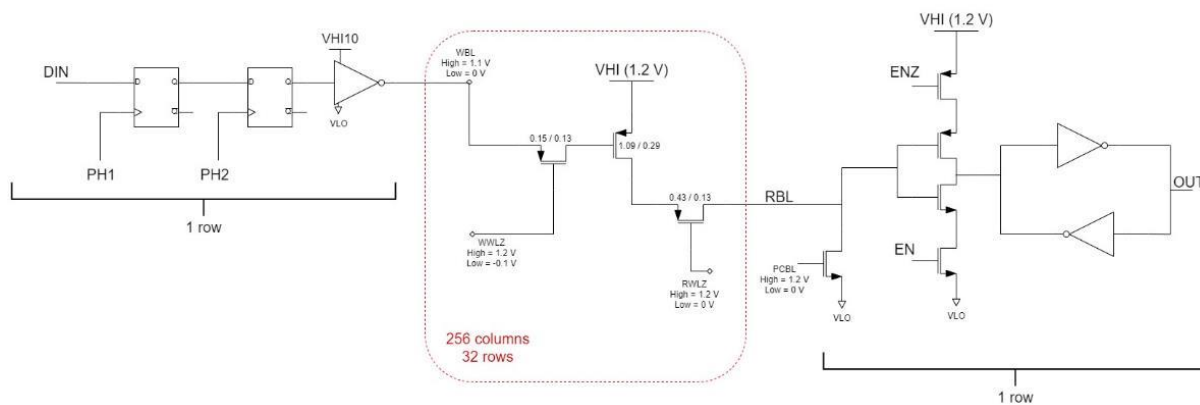
	Analog (half)		Digital		Low Density module				High Density module				Comments
					Analog		Digital		Analog		Digital		
	(mA)	(mW)	(mA)	(mW)	(A)	(W)	(A)	(W)	(A)	(W)	(A)	(W)	
<b>Low power mode</b>	<b>63</b>	<b>76</b>	<b>83</b>	<b>100</b>	<b>0,378</b>	<b>0,456</b>	<b>0,249</b>	<b>0,3</b>	<b>0,756</b>	<b>0,912</b>	<b>0,498</b>	<b>0,6</b>	RUN = 0
Default config	260	312	127	153	1,56	1,872	0,381	0,459	3,12	3,744	0,762	0,918	Not trimmed parameters
<b>trimmed</b>	<b>260</b>	<b>312</b>	<b>127</b>	<b>153</b>	<b>1,56</b>	<b>1,872</b>	<b>0,381</b>	<b>0,459</b>	<b>3,12</b>	<b>3,744</b>	<b>0,762</b>	<b>0,918</b>	Adjusted pedestals, threshold, gain ...
vbi11	300	360	127	153	1,8	2,16	0,381	0,459	3,6	4,32	0,762	0,918	trim_vbi_pa=11 (default is 7)
vbi15	330	396	127	153	1,98	2,376	0,381	0,459	3,96	4,752	0,762	0,918	trim_vbi_pa=15
50% 10ch	280	336	134	161	1,68	2,016	0,402	0,483	3,36	4,032	0,804	0,966	trimmed conf. + 50% TOA in 10 channels per half
50% all	325	390	154	185	1,95	2,34	0,462	0,555	3,9	4,68	0,924	1,11	trimmed conf. + 50% TOA in all channels
LowBuf	215	258	127	153	1,29	1,548	0,381	0,459	2,58	3,096	0,762	0,918	Low power ADC buffer
LowBuf + vbi11	255	306	127	153	1,53	1,836	0,381	0,459	3,06	3,672	0,762	0,918	
LowBuf + vbi15	290	348	127	153	1,74	2,088	0,381	0,459	3,48	4,176	0,762	0,918	

## Spec < 15 mW / channel

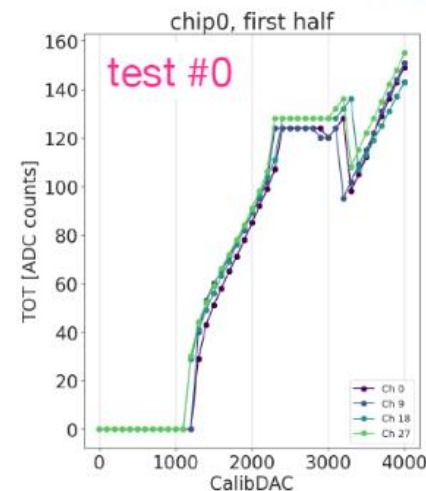
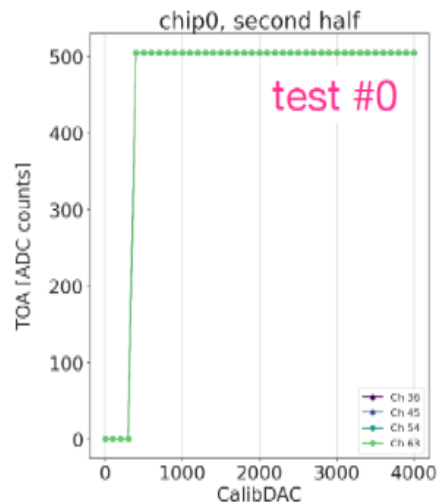
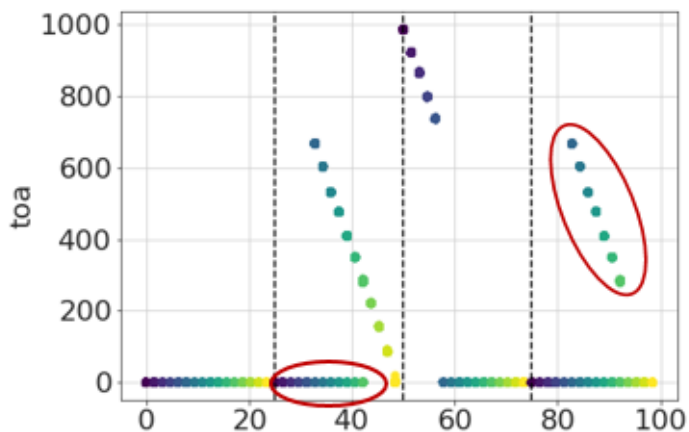
- Low power mode: 3,5 mW / channel
  - Default config : ~10,8 mW /channel
  - With 50 % toa events in 50 % channels: 11,5 mW / channel
  - With maximum preamp. current : **11,8 mW / channel**
- **H2GCROC3:**

	Gain_conv	Analog 1.2		Analog 2.5 (2.41)		Digital 1.2		Comments
		mA	mW	mA	mW	mA	mW	
Low power mode	15	104.30	125.16	27.90	67.24	112.70	135.24	
Default config		353.20	423.84	136.80	329.69	123.00	147.60	
vbi_pa 48		356.30	427.56	116.80	281.49	125.90	151.08	dacb_vbi_pa = 48
vbi_pa 63		356.50	427.80	94.80	228.47	127.00	152.40	dacb_vbi_pa = 63
10 ch TOA		357.00	428.40	136.60	329.21	124.80	149.76	toath = 65, 10 channel per half unmasked
all ch TOA		359.00	430.80	136.50	328.97	126.30	151.56	toath = 65, all channels unmasked
Default config	2	376.00	451.20	128.60	309.93	135.30	162.36	
vbi_pa 48		374.00	448.80	108.90	262.45	134.50	161.40	dacb_vbi_pa = 48
vbi_pa 63		366.50	439.80	87.30	210.39	135.40	162.48	dacb_vbi_pa = 63
10 ch TOA		375.20	450.24	128.60	309.93	135.30	162.36	toath = 65, 10 channel per half unmasked
all ch TOA		376.20	451.44	128.80	310.41	131.10	157.32	toath = 65, all channels unmasked

- **Large majority of 1 > 0 bitflips**
  - Not a classical leakage effect
  - Better (almost perfect) at low temperature and/or low digital power supply
- **RBL node has been identified as culprit**
  - Lower capacitance on RAM2 (due to the shrink from 512 to 32)
  - Reproduced in simulation
  - Force VHI10\_0 to VDDD corrects the misbehaviour
    - No bitflips at all whatever the temperature and power supply value
    - No problem with multi consecutive L1A
- **Corrected for next version, ROC3b**, add capacitance on this node and possibility to force VHI10\_0 to VDDD
- Has been implemented in HKROC1, first measurements show the fix works

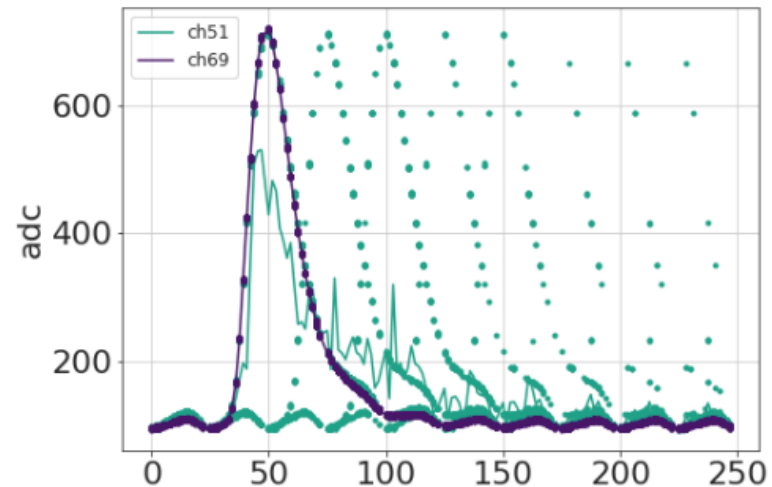
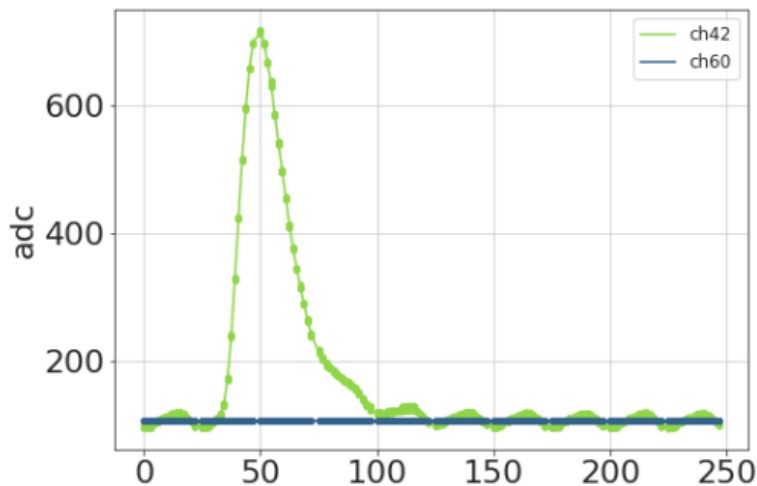


- **Issue 2.1: TOA data in the wrong BXs**
  - Error localization in the start of the latency buffer of the TDC FiFo. A double clock gating causes a glitch in the zone where the 40MHz clock is at 0
  - This effect is reproduced in simulation and **will be corrected in HGCROC3b**
- **Issue 2.2: TOA data for all channels from the same half are stuck to 504 (0b 01 1111 000)**
  - Infrequent effect, impossible to make reproducible
  - Resetting the chip resolves the issue
  - Reproduced in simulation: the Master DLL is not properly locked
  - **Has been fixed by changing the startup sequence**
- **Issue 2.3: Strange (faster) TDC measurement**
  - Happens more often than issue 2.2
  - Completely removed after tuning DLL parameters (Charge pump current)
  - **Has been fixed by changing the startup sequence**

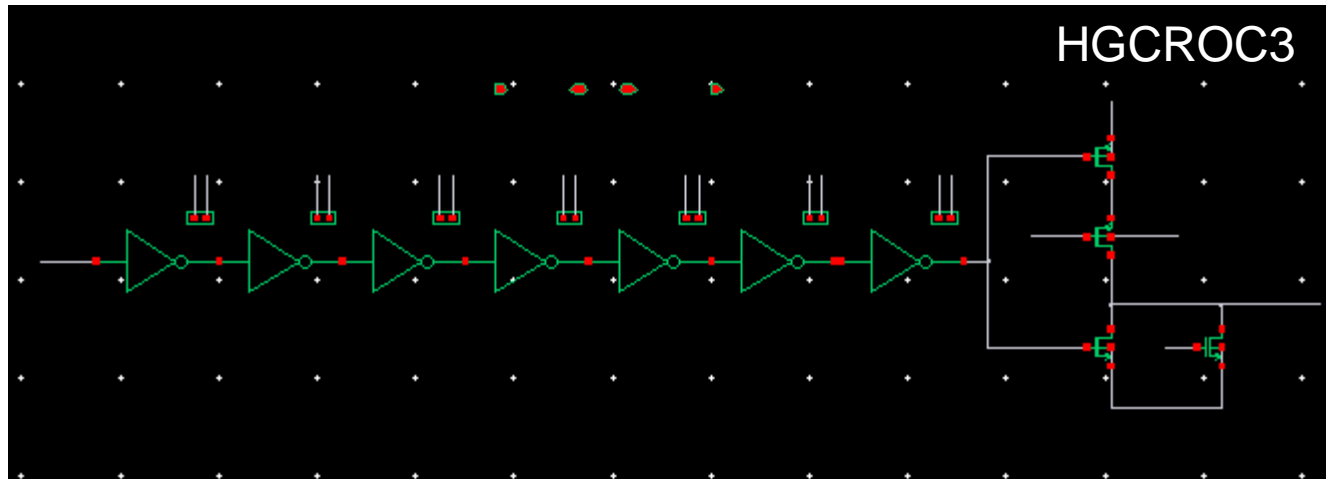


- **Flat ADC or Multiple ADC**

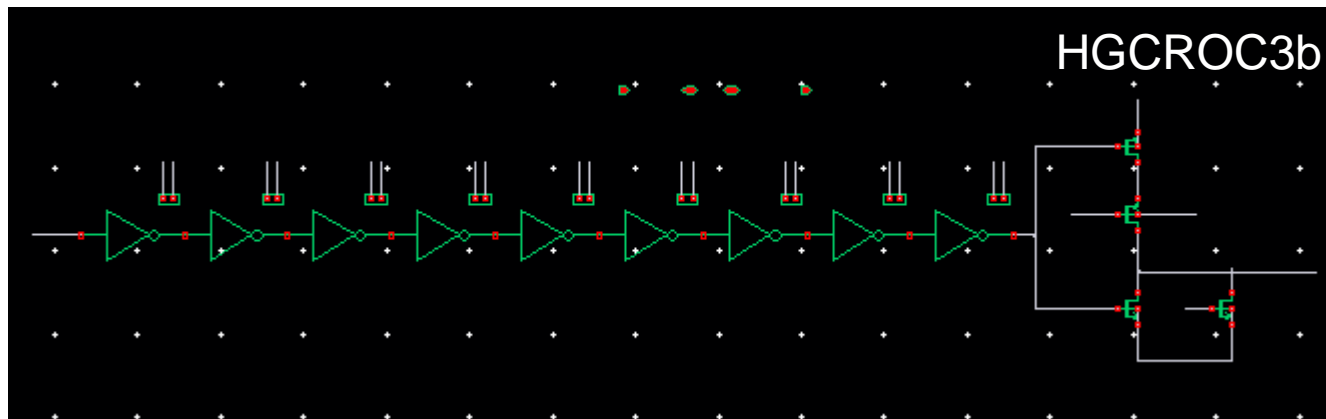
- Already in HGCROC2, although less often
  - More easily resolved by tuning conversion time
  - HGCROC2 run faster than HGCROC3 which seems more in the typical region
- The ADC does not convert at 40 MHz
- Sensitive to ADC settings (conversion time), temperature, digital power supply
- ~ 5 % of the channels at room temperature, but not Gaussian distribution at all
- RC-extracted view reproduces both flat ADC and Multiple ADC effect (6% bad channels against ~ 5% in measurement)
- **Will be corrected in HGCROC3b (Next slide)**
- **Correction proved to work in HKROC1**





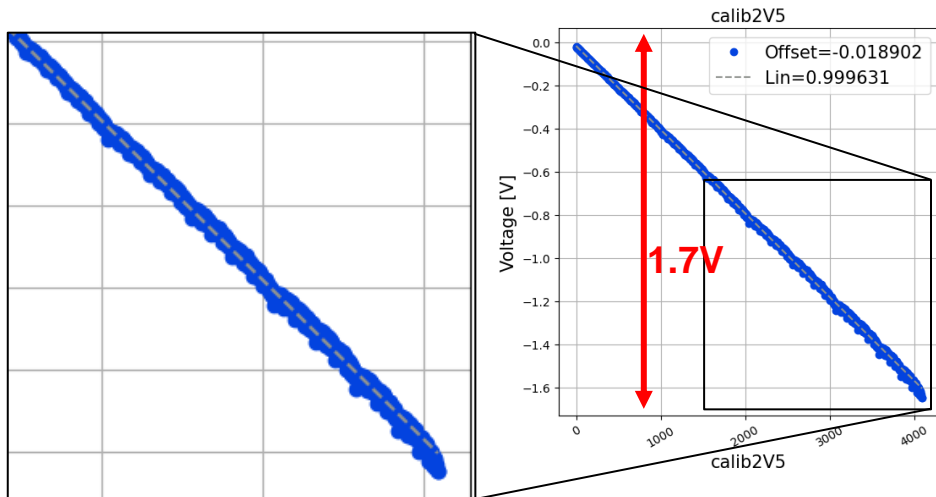


Simulations Monte-Carlo + process corners done

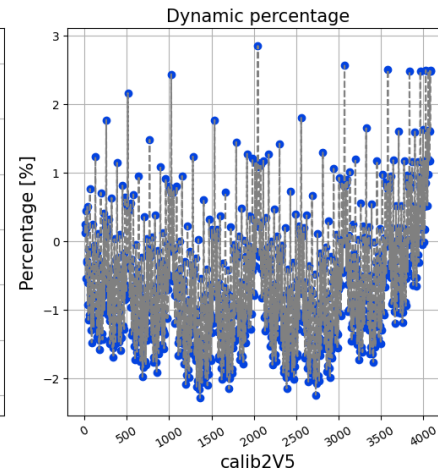
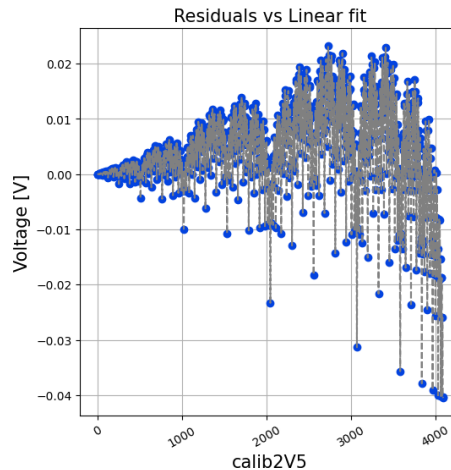


Effects disappear in all corner and MC simulation with this change

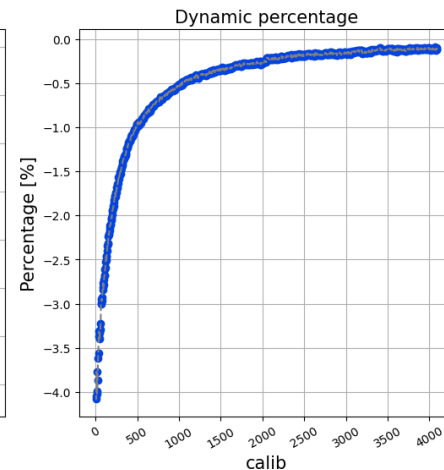
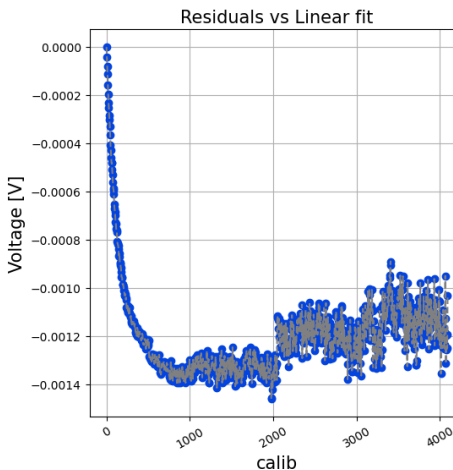
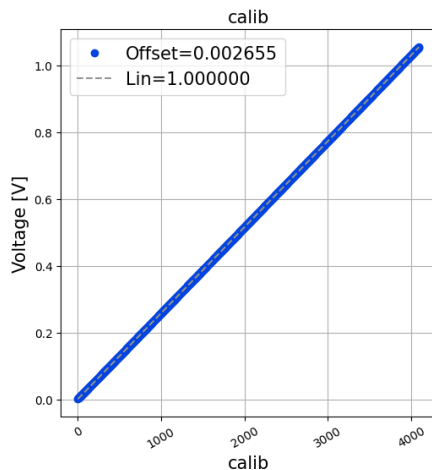
**Nonlinearities** calibdac2V5 especially for larger values.  
 Dynamic range up to 1.7 V that corresponds to 0 to 200pC injection.



Keithley measurements Roc 03

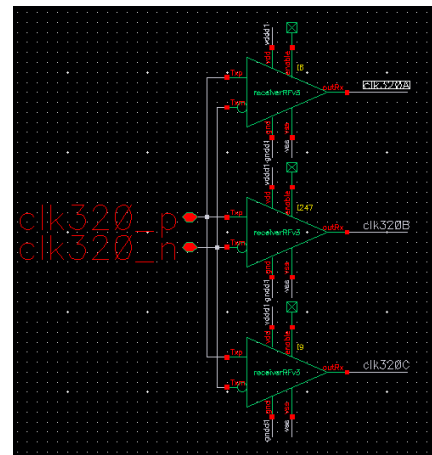
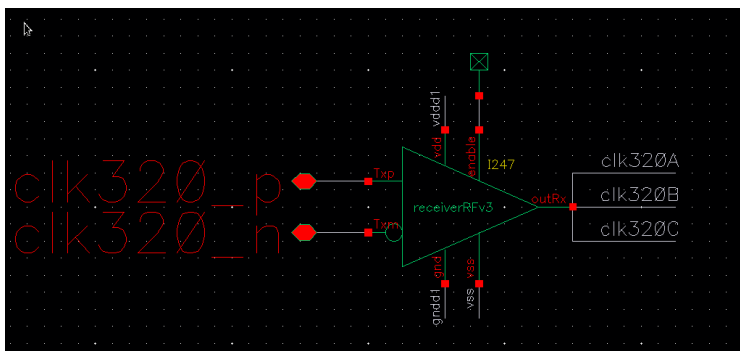


**1.2V Calib DAC**  
 for injection into  
 the PA doesn't  
 present  
 nonlinearities:

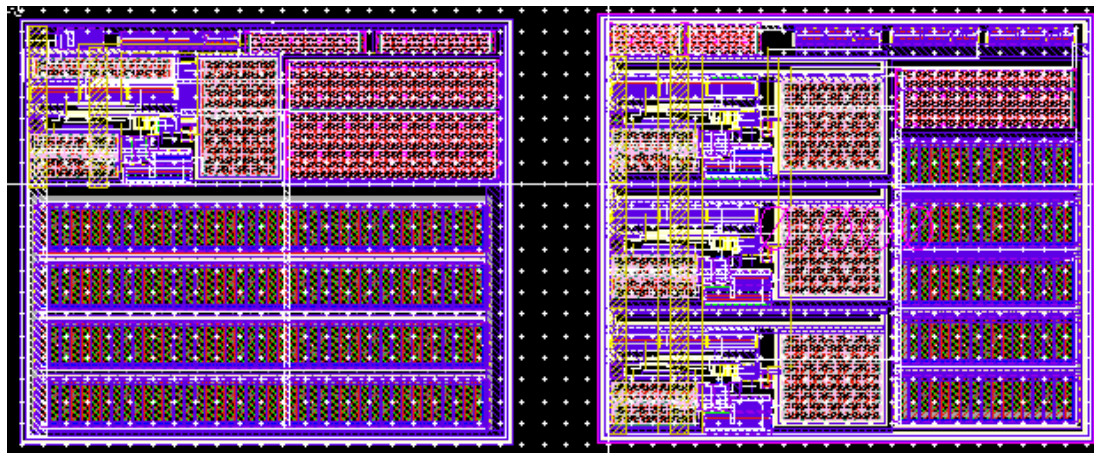


- **SEU mitigation**

- Triplication of CLPS receivers for CK320 and FCMD
- Enable pin removed...



Old



New

- Capacitance added on sensitive ENABLE/startup nodes (bandgap....). Look/simulate all these nodes in schematic !
- M7 shielding of ctest line to avoid crosstalk from internal injection

- [1] CERN (2021). *CMS Detector*. [Online]. Available: <https://portail.polytechnique.edu/omega/fr/omega/recherche/cms-hgcal>
- [2] CMS Collaboration (2018). *The Phase-2 Upgrade of the CMS endcap calorimeter*. CERN-LHCC-207-023, Vols. CMS-TDR-019, pp. 1-364.
- [3] CERN (2016). *Interactive Slice of the CMS detector*. CERN Document Server. [Online]. Available: <https://cds.cern.ch/record/2205172/files/CMS%20Slice.gif?version=1>
- [4] D. Thienpont (2020). *H2GCROC2/2A: architectural overview*. OMEGA Microelectronics. [Online]. Available: [https://edms.cern.ch/ui/file/2133536/1/ASIC\\_parameters\\_HGCROC\\_for\\_SiPM.pdf](https://edms.cern.ch/ui/file/2133536/1/ASIC_parameters_HGCROC_for_SiPM.pdf)
- [5] CMS collaboration (2020). *Handling large data volumes of CMS High Granularity Calorimeter (HGCal)*. [Online]. Available: [https://www.niser.ac.in/daehep2020/talkposter/Alpana\\_Alpana\\_TLK\\_124\\_195.pdf](https://www.niser.ac.in/daehep2020/talkposter/Alpana_Alpana_TLK_124_195.pdf)
- [6] K. Briggli, H. Chen, D. Schimansky, W. Shen, V. Stankova, and H.C. Schultz-Coulon, (2016) “*KLauS: A low power Silicon Photomultiplier charge readout ASIC in 0.18 UMC CMOS*,” *Journal of Instrumentation*, vol. 11, no. 3.
- [7] Hamamatsu. “*MPPC (multi-pixel photon counter) S14160-1310PS/-1315PS/-3010PS/-3015PS*”. Hamamatsu 2020. [Online]. Available: [https://www.hamamatsu.com/resources/pdf/ssd/s14160-1310ps\\_etc\\_kapd1070e.pdf](https://www.hamamatsu.com/resources/pdf/ssd/s14160-1310ps_etc_kapd1070e.pdf)
- [8] E. Vernazza (2022). *HGCROCv3 TID Irradiation Test at CERN*. CMS Collaboration. [Online] <https://indico.cern.ch/event/1206678/contributions/5075310/attachments/2521753/4336295/TID%20Irradiation%20test%20September.pdf>
- [9] OMEGA (2023). *H2GCROC TID irradiation test*. CMS Collaboration. [Online] [https://indico.cern.ch/event/1277080/contributions/5366950/attachments/2630948/4550440/H2GCROCv3\\_TID\\_april\\_1\\_2.pdf](https://indico.cern.ch/event/1277080/contributions/5366950/attachments/2630948/4550440/H2GCROCv3_TID_april_1_2.pdf)
- [10] CERN (2022). *Obelix*. EP-ESE irradiation system. [Online] [https://espace.cern.ch/project-xrayese/\\_layouts/15/start.aspx#/ObeliX/Forms/AllItems.aspx](https://espace.cern.ch/project-xrayese/_layouts/15/start.aspx#/ObeliX/Forms/AllItems.aspx)
- [11] CERN (2022). *AsteriX*. EP-ESE irradiation system. [Online] [https://espace.cern.ch/project-xrayese/\\_layouts/15/start.aspx#/AsteriX/Forms/AllItems.aspx](https://espace.cern.ch/project-xrayese/_layouts/15/start.aspx#/AsteriX/Forms/AllItems.aspx)
- [12] E. Vernazza (2022). *HGCROCv3 SEE Irradiation Test*. CMS Collaboration. [Online] <https://indico.cern.ch/event/1180878/contributions/4962671/attachments/2482246/4261474/HGCROCv3%20SEE%20Irradiation%20test.pdf>
- [13] E. Vernazza (2023). *Proton irradiation testing of HGCROC3*. CMS Collaboration. [Online] <https://indico.cern.ch/event/1258903/contributions/5287985/attachments/2601542/4492136/SEE%20Proton%20Irradiation.pdf>
- [14] P. P. Calò, F. Ciciriello, S. Petrigani, C. Marzocca (2019). *SiPM readout electronics*. *Nuclear Inst. and Methods in Physics Research*, vol. A, no. 926, pp. 57–68.